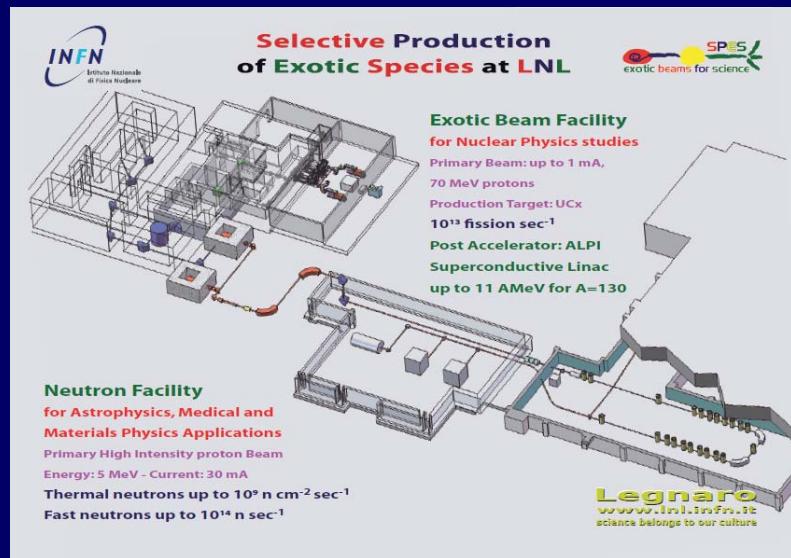
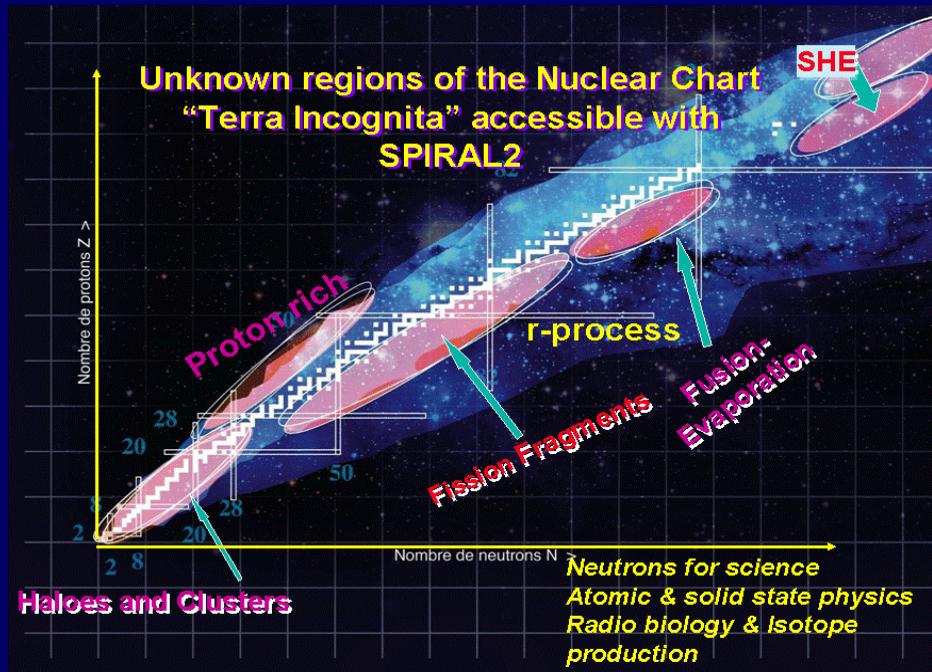


FAZIA detector for Nuclear (Thermo)Dynamics Physics using RIBs factories

from Phase1 to Phase2



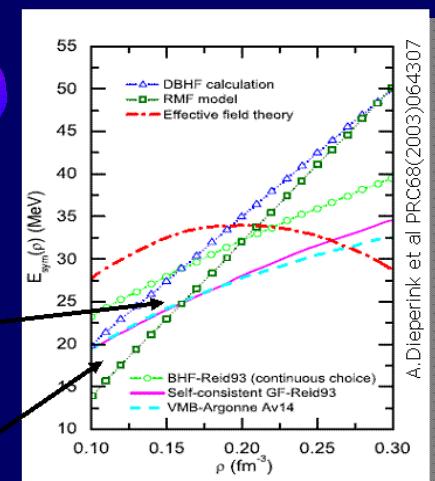
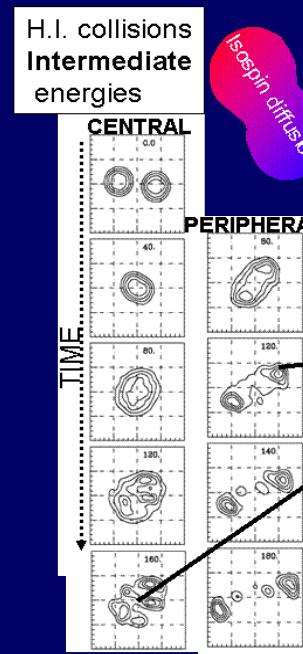
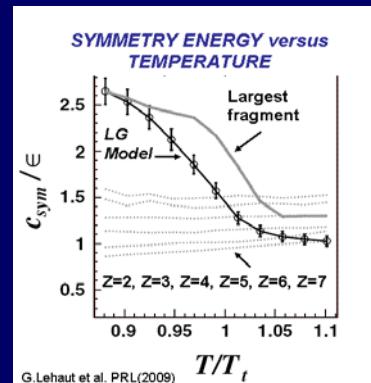
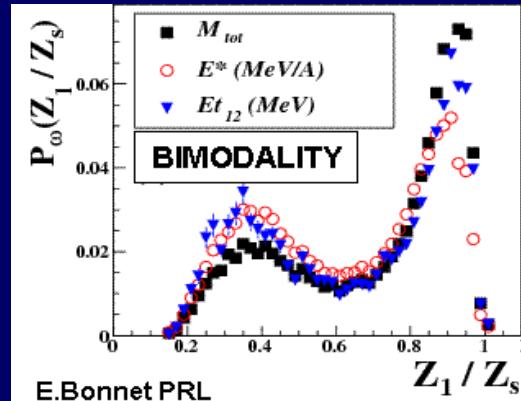
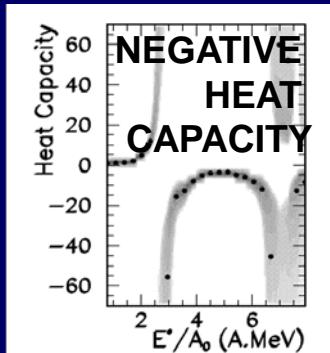
GANIL, LNS, LNL



FAZIA: Scientific case

Nuclear Equation Of State N/Z dependence $E(\rho, T, (N-Z)/A)$

- Nuclear Matter first Phase Transition (“Liquid-Gas”)
- Nuclear level densities and Limiting temperature
- Symmetry Energy (density and temperature dependence)



NEED OF (A,Z) Identification



GANIL, LNS, LNL





LOI 18

Letter of Intent for SPIRAL 2

Title: Dynamics & Thermodynamics of exotic nuclear structures

Spokesperson(s) (*max. 3 names, laboratory, e-mail - please underline one corresponding spokesperson*):

F. Gulminelli (LPC-ENSICAen, Caen, France, e-mail: gulinelli@ensicaen.fr)

G. Poggi (INFN & University, Florence, Italy, e-mail: poggi@fi.infn.it)

G. Verde (INFN, Catania, Italy, e-mail: giuseppe.verde@ct.infn.it)

GANIL contact person

J. Frankland (GANIL, Caen, France)

Collaboration (names and laboratories)

FRANCE:

IPNO (Orsay): E. Bonnet, B. Borderie, E. Galichet, N. Joly

GANIL (Caen): A. Chbihi, J. Frankland, J. Moisseyk

LPC-ENSICAen (Caen): S. Barlini, R. Bouga, C. Gobin, J. Lehaut, J. M. Llopart, J. M. Pochet, J. P. Rodriguez, O. Lopez, B. Tamain, E. Vient

IPNL (Lyons)

INDIA:

VECC (Calcutta)

Banerjee, Roy

ITALY:

Bologna (CERN)

Marini, G. (Lecce)

Catania (Lecce)

Catania (Lecce)

Firenze (I)

Olmi, G. Pasquini (I)

Puglisi, S. Piantelli, A. Stefanini (I)

LNL (INFN): M. La Commara, M. Degerlier, F. Gramigna, V. Kravchuk (I)

Napoli (INFN & University): M. La Commara, A. Ordine, E. Rosato, G. Spadaccini, M. Vigilante

POLAND:

Krakow (Jagiellonian University): A. Becla, T. Kozik, Z. Sosin, A. Wieloch

Katowice (Silesian University): A. Grzeszczuk, S. Kowalski, W. Zipper

Warsaw (Warsaw University): A. Kordyasz, E. Piasecki

ROMANIA:

M. Preda, M. Radescu

Salmeron, M. Salmeron

« ... by apparatuses are available at present, the new detector system FAZIA will be indispensable in future studies at SPIRAL2... »

(Annexe of general recommendations of the SAC of SPIRAL2, 2006)

72 persons – 19 institutions – 8 countries

NEED OF (A,Z) Identification

FAZIA LOI SPES



SPES-2015 FAZIA config. **1180** detectors

Beam current: **132Sn** 3.3×10^7 pps

target thickness: 0.5 mg/cm²

Reaction Xsection 3.2 barn; DIC Xsection 2.2 barn

DIC total rate: 330 Hz

2-body channel:

MC estimated eff. for QP & M>=1: 10%

Request: 10^7 dissipative events in the most central impact parameters ($b/b_{gr} < 0.5$)

Rate for wanted events: about 4.6days

(this gives 35 million wanted elastic-Sn on the 3deg forward

Telescope, 91% efficiency)

3-body channel (the split of the QP)

MC estimated eff. for (FF1& FF2 & M>=1 LCP): 10%

3body rate assumed to be 20% of DIC

Request: the previous 10^7 binary events

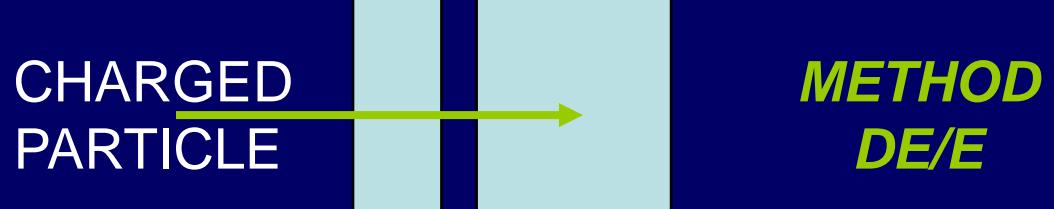
Rate for 3-body events 7Hz --> 2.7 million 3body events in 4.6days

NEED OF (A,Z) Identification

A and Z Identification

HEAVY-IONS COLLISIONS → IDENTIFY THE REACTION PRODUCTS

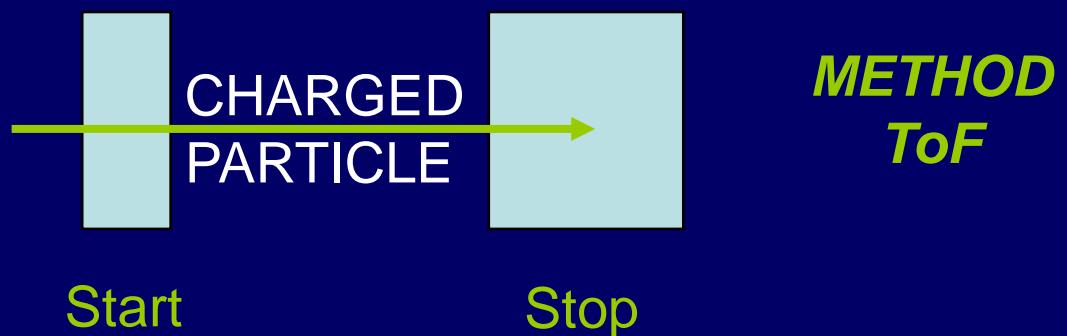
Energy is measured
Z identification
A identification (for low Z)
For particles stopped in the
first DE no identification



METHOD
DE/E

$$\text{Energy loss} = f(A, Z)$$

Energy is measured
Velocity is measured
A identification
For particles stopped in the
first DE no Z identification



METHOD
ToF

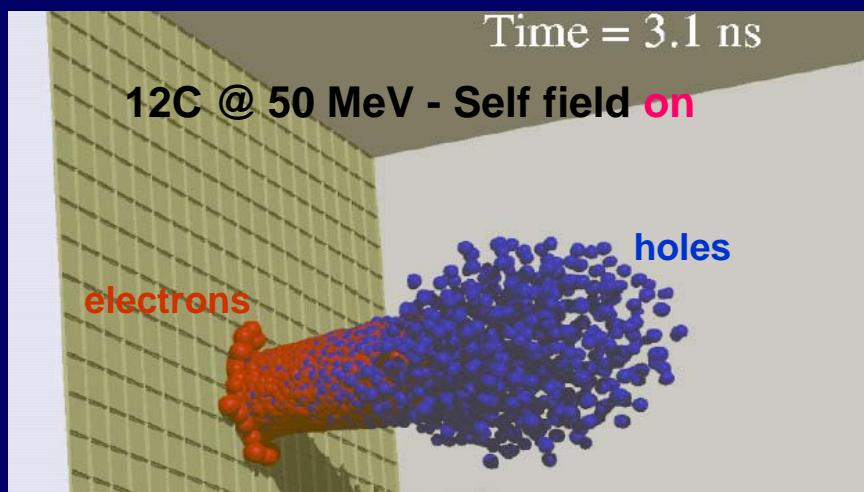
Time, long flight path

A and Z Identification

HEAVY-IONS COLLISIONS → IDENTIFY THE REACTION PRODUCTS

1) RANGE = $f(A, Z)$

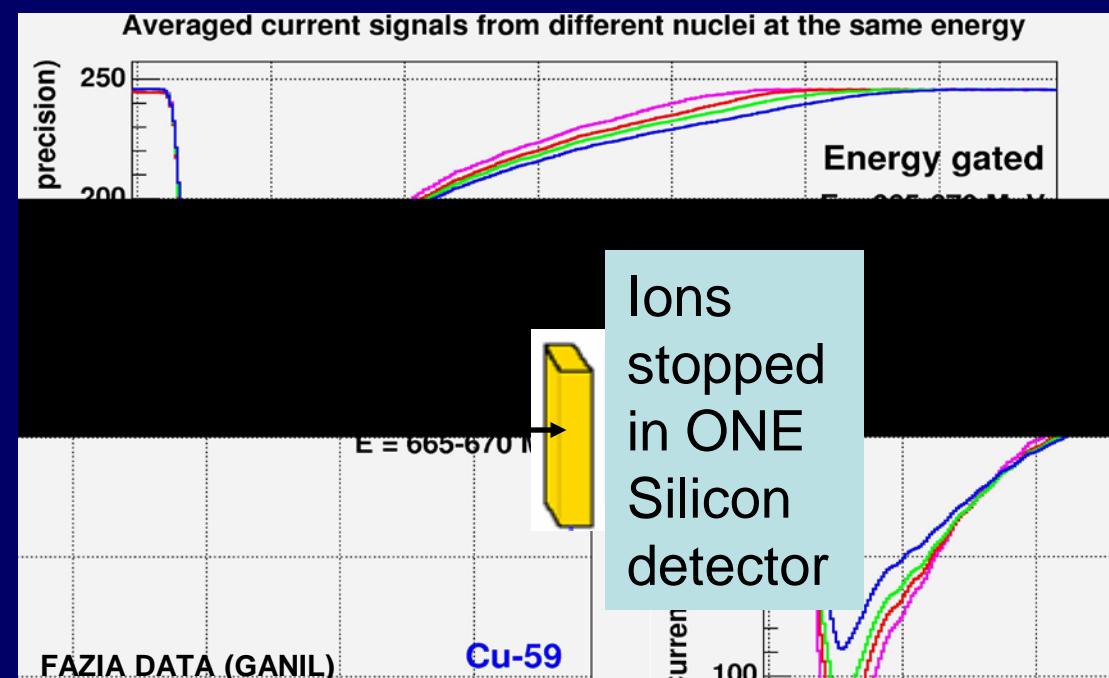
2) Plasma erosion
process = $f(A, Z)$



A simulated plasma column for ^{12}C @ 50 MeV

Self field on (L.Bardelli, FAZIA)

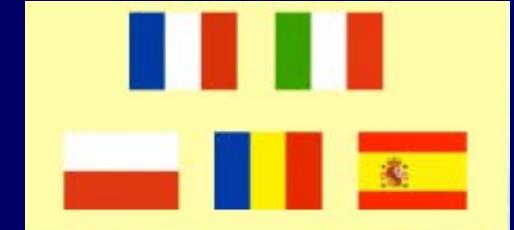
USE THE ELECTRONIC SIGNAL
FOR (A,Z) IDENTIFICATION:
“Pulse Shape Discrimination”



FAZIA collaboration

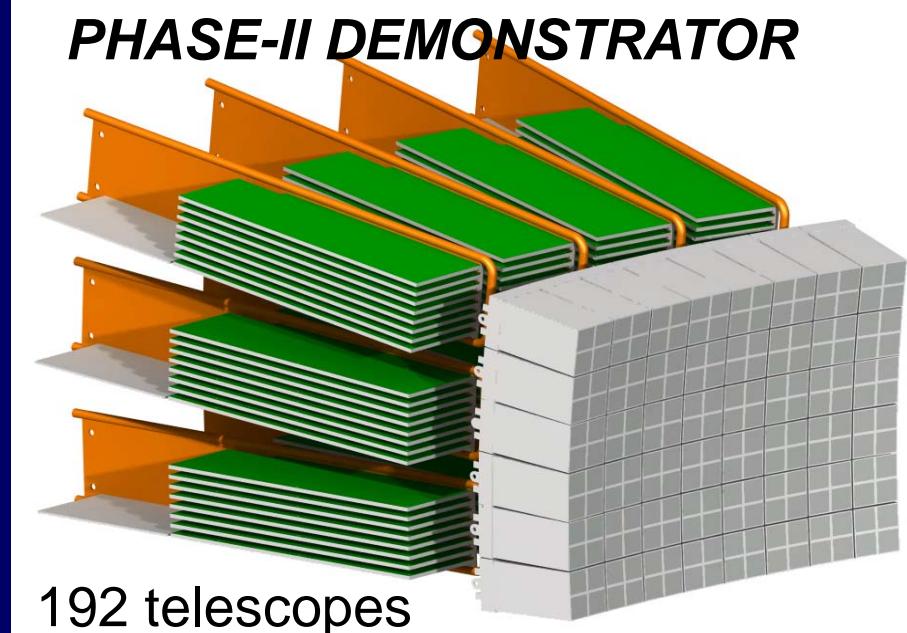
An R&D project supported by Spiral2PP and LEA-colliga.

It is aimed at designing a new-generation detector for charged particles, suited for Isospin Physics to be done *with n-poor and n-rich ions* at Radioactive Beam Facilities like Spiral2 and SPES (and EURISOL)



FAZIA Working Groups

1. Modeling current signals and Pulse Shape Analysis
2. Physics cases
3. Front End Electronics
4. Acquisition
5. CsI(Tl) crystals
6. Single Chip Telescope
7. Design, Detector, Integration and Calibration

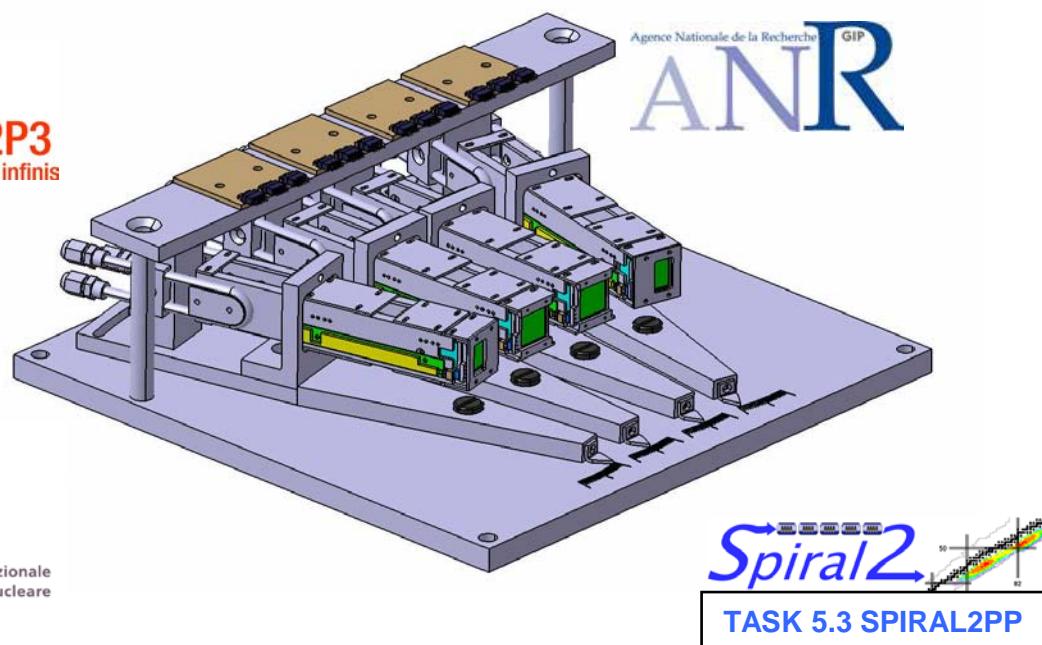


FAZIA R&D

1) Experiments with single silicon-detector (Tandem-Orsay, LISE-GANIL) Jan. 2006

2) Experiments with single silicon-detector & strip-detector (CIME/GANIL) & LNL (channeling & uniformity) Jan. 2007

3) Prototypes (phase1)



+ nTD strip-detector

LNL-experiment Jan. 2008

Jan. 2009

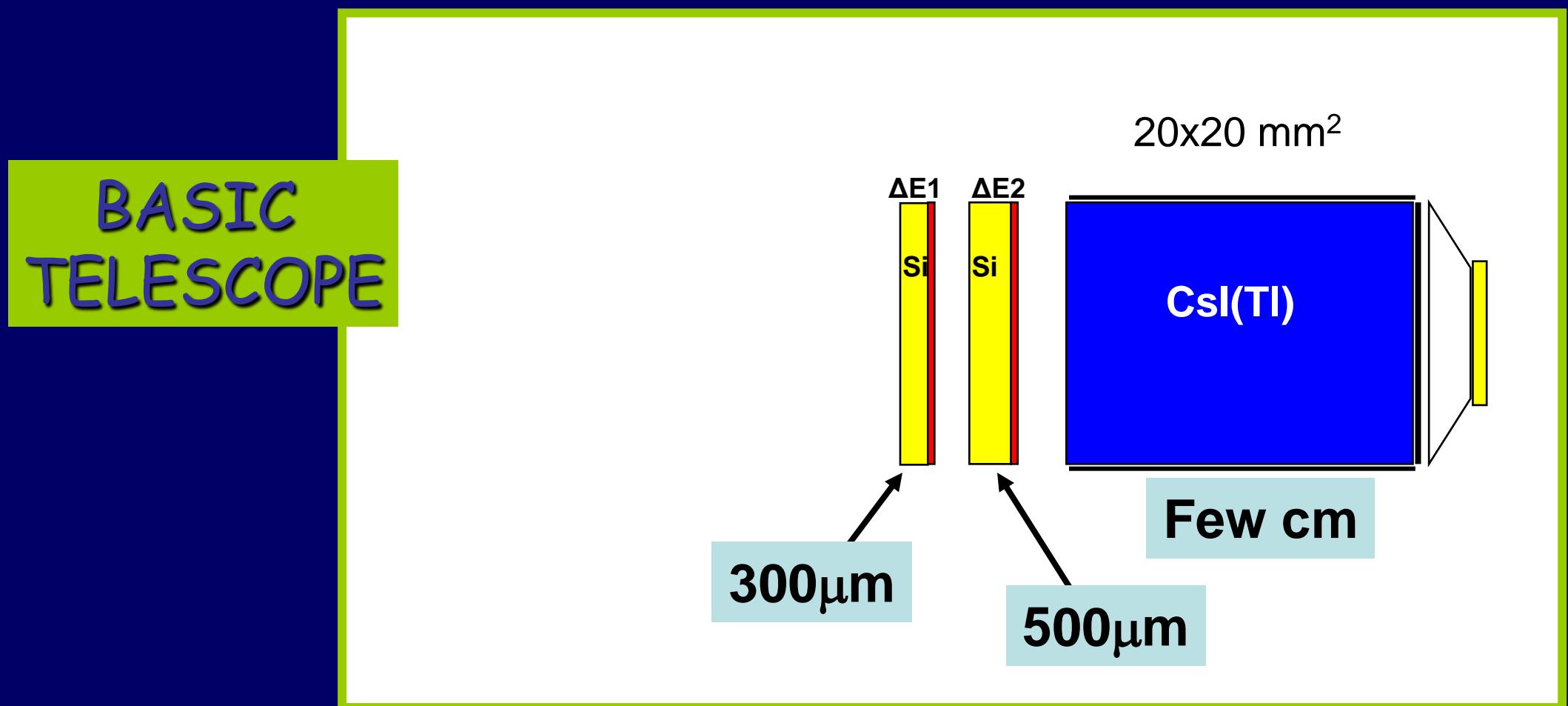
LNS-test
LNS-experiment

Jan. 2010

GANIL-experiment Jan. 2011

LNS-experiment

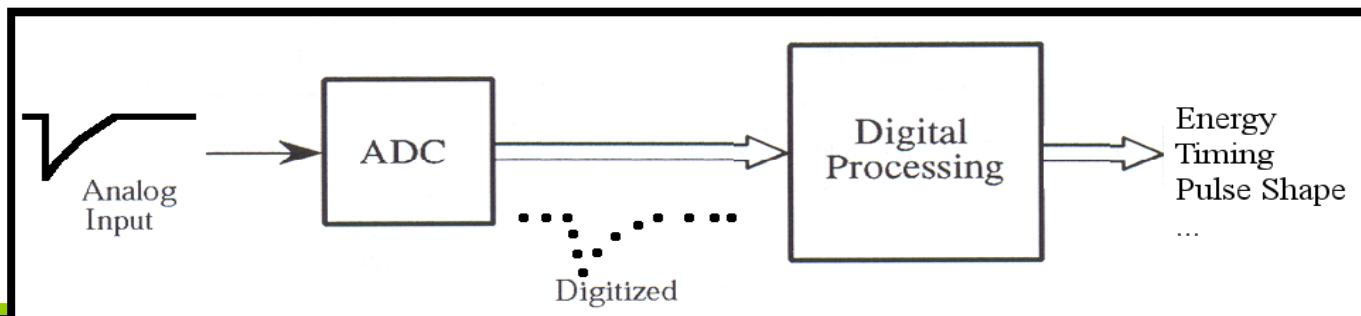
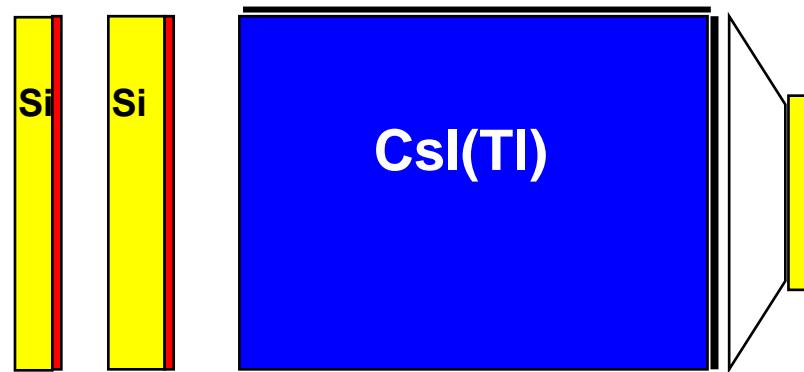
FAZIA detector



FAZIA detector

**BASIC
TELESCOPE**

**Identify ions with in one silicon detector
low id. Thresholds (digitized signals)**



FAZIA PhaseI-R&D

RECIPE FOR HIGH QUALITY CHIPS

1 – DOPING UNIFORMITY

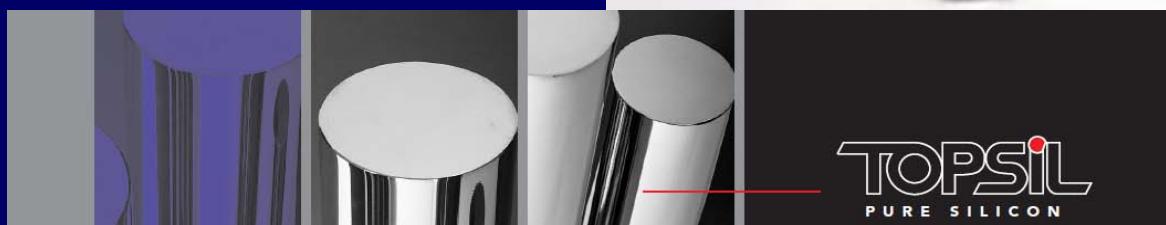
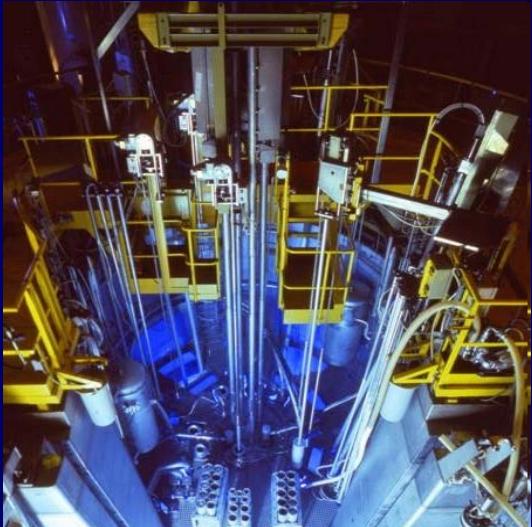
Ingot selection from the producer, controlled doping (at about $\rho=3000$ ohm.cm) and use of nTD technology for best uniformity (+/- 0.5 %)

2 – AVOID (as far as possible) CHANNELING

Ingot orientation and choice of the cut along special 'random' directions (7deg to <100>); slices of 300 and 500 microns

FAZIA PhaseI-R&D

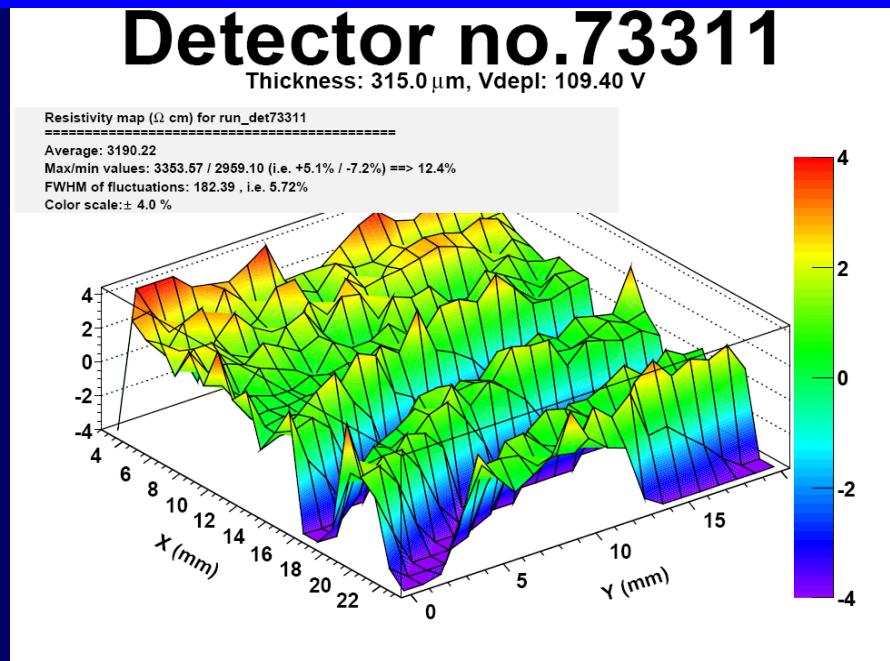
DOPING UNIFORMITY



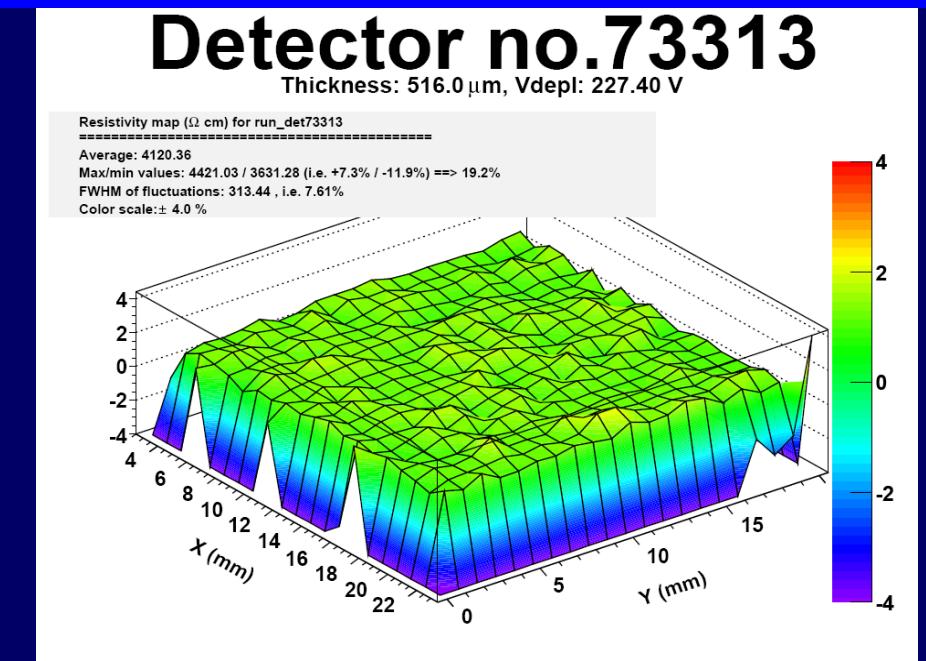
FAZIA PhaseI-R&D

non-homogeneity in the electric field inside the detector (doping) may have a severe impact over the Pulse Shape Discrimination capabilities:

A typical detector: ~9% non-uniformity

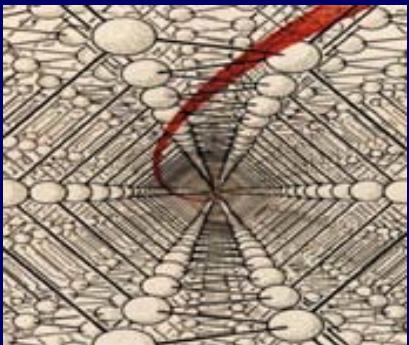


A very good detector: ~1% non-uniformity



IMPROVEMENT IN DOPING UNIFORMITY

FAZIA PhaseI-R&D



CHANNELING

Energy loss in an crystal (aligned configuration):

“perfect” channeling

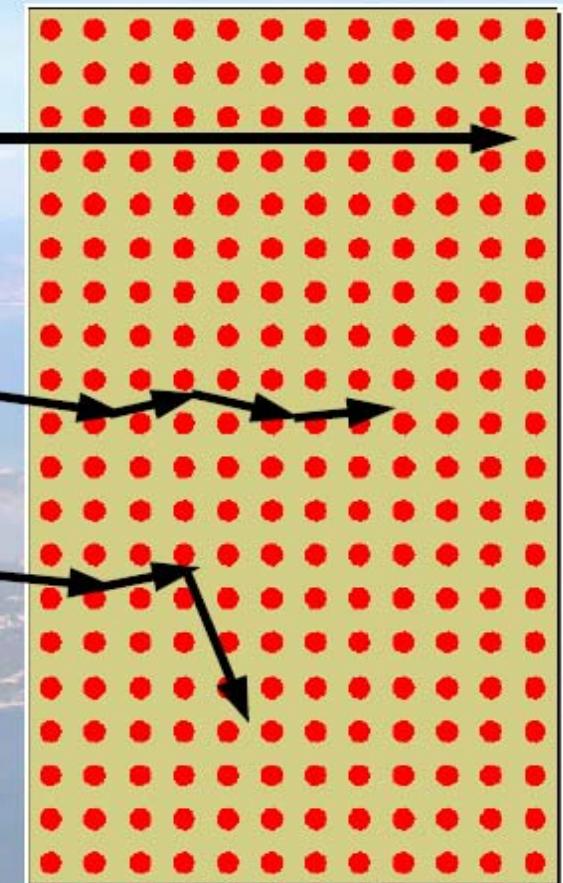
long range, low average dE/dx

shorter range, higher average dE/dx

channeling + de-channeling
even shorter range, higher average dE/dx

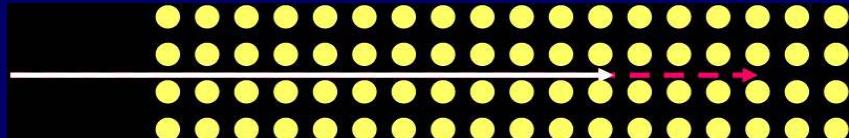
many possible trajectories leading to
different ranges and/or average dE/dx

resolution loss!

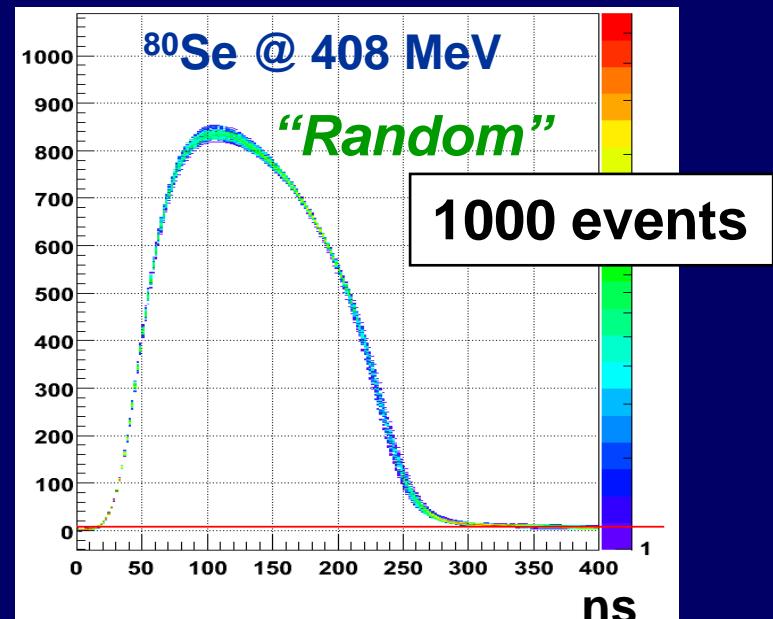
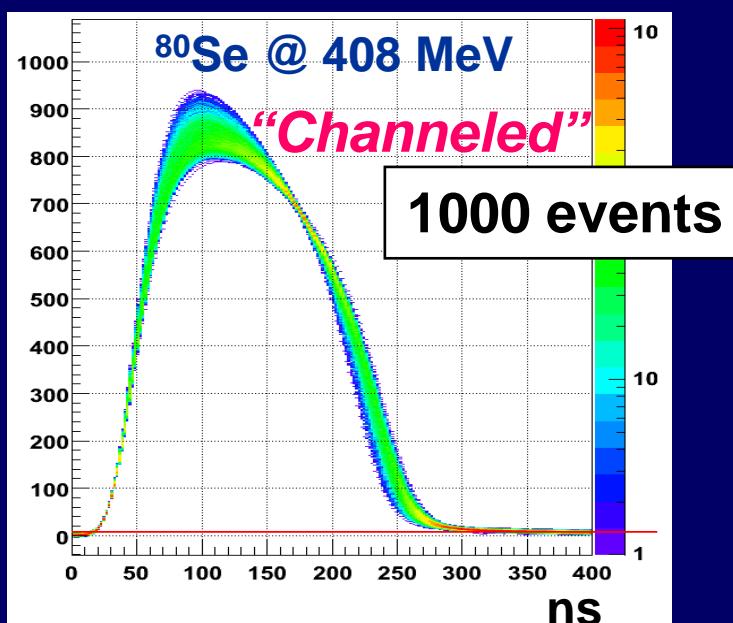
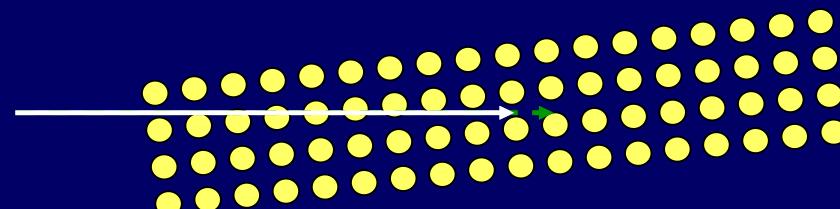


FAZIA PhaseI-R&D

“Channeled”



“Random”



IMPROVEMENT IN SIGNAL DISPERSION

FAZIA data (LNL)

FAZIA PhaseI-R&D

RECIPE FOR HIGH QUALITY CHIPS

1 - UNIFORMITE DU DOPAGE

Ingot selection from the producer, controlling doping (at about $\rho=3000$ ohm.cm) and use of n-Tech technology for best uniformity (+/- 0.5 %)

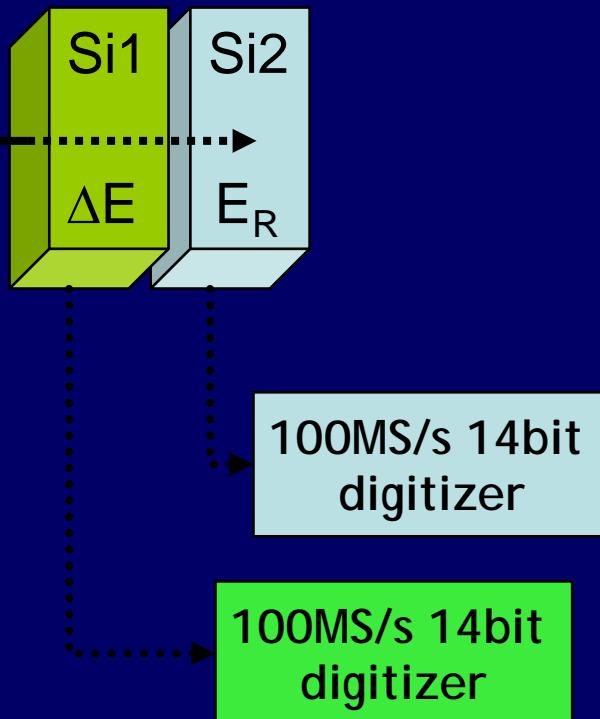
2 – EVITER AU MIEUX LA CROISSANCE

Ingot orientation and choice of the cut along special 'random' sections (7deg to <100>); slices of 300 and 500 mm

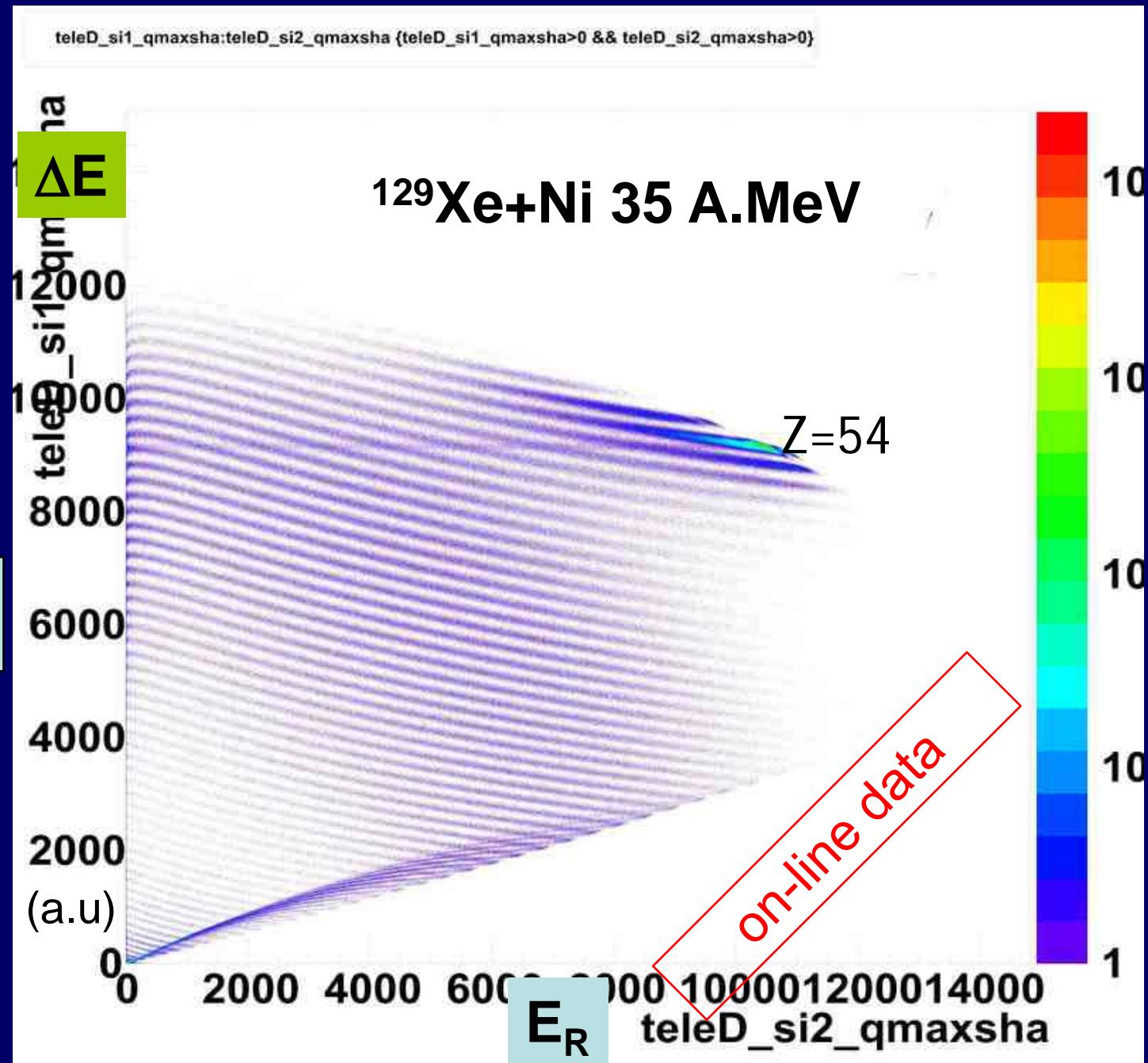
IN THE FOLLOWING THE RECIPE HAS BEEN APPLIED

FAZIA PhaseI-R&D

*Usual
DE/E
technique*

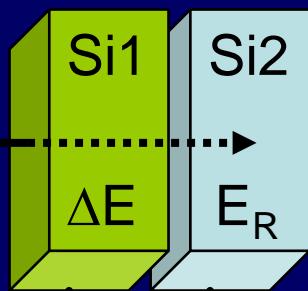


FAZIA data (LNS)



FAZIA PhaseI-R&D

*Usual
DE/E
technique*

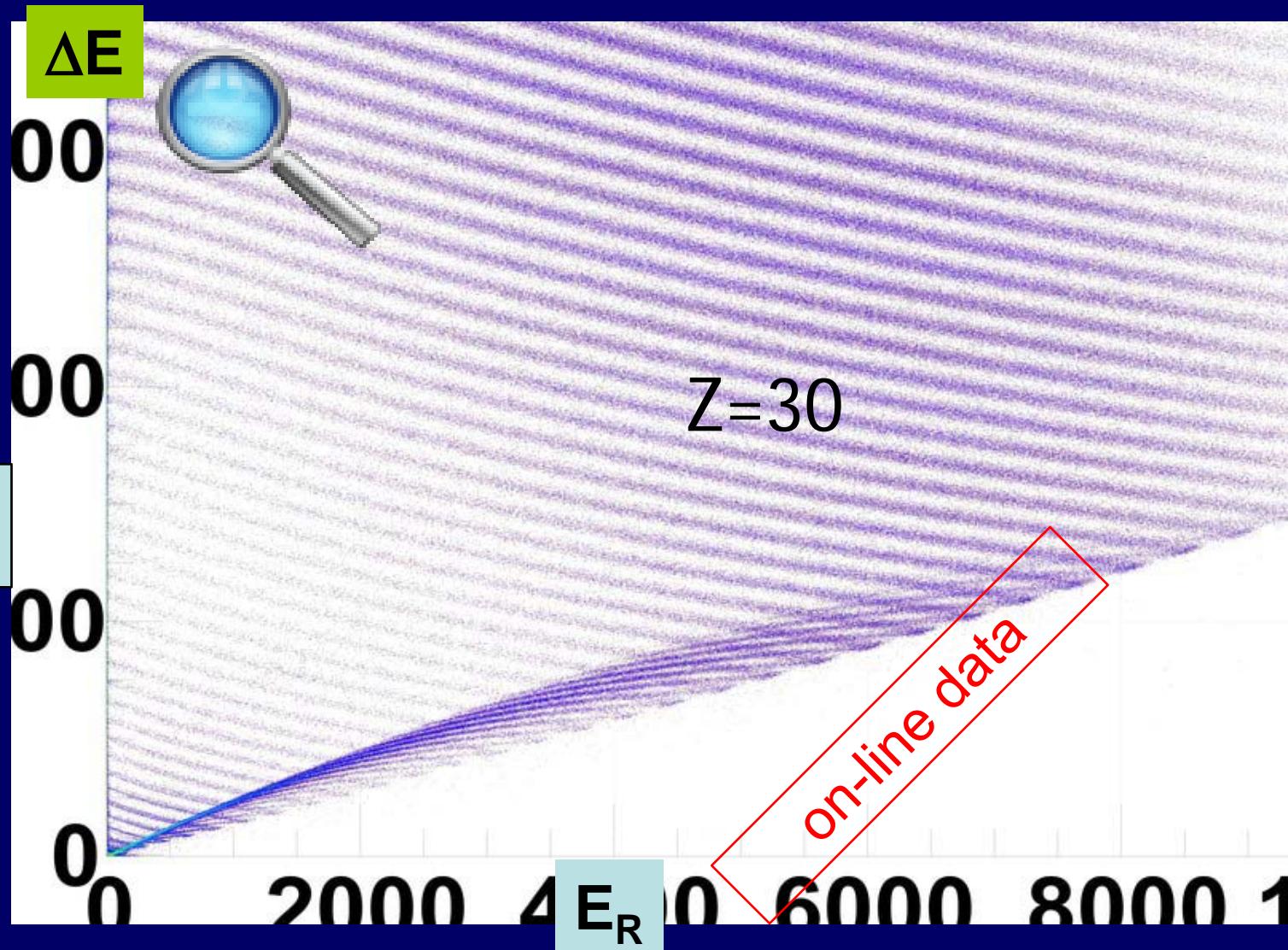


100MS/s 14bit
digitizer

100MS/s 14bit
digitizer

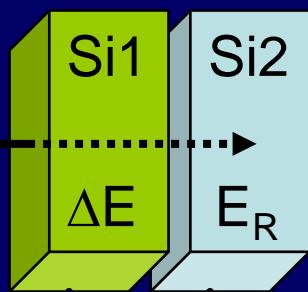
FAZIA data (LNS)

ZOOM



FAZIA PhaseI-R&D

*Usual
 $\Delta E/E$
technique*



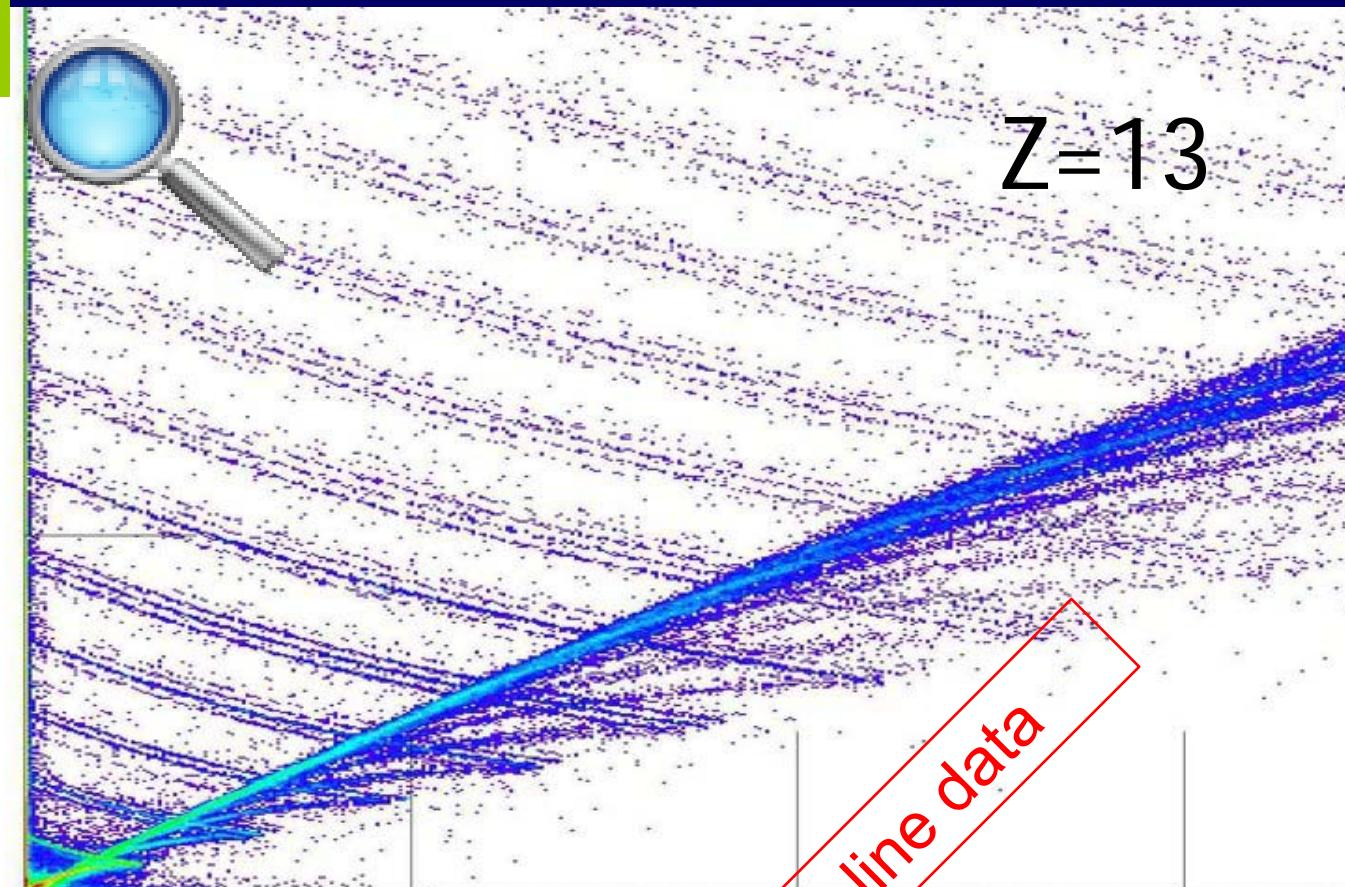
100MS/s 14bit
digitizer

100MS/s 14bit
digitizer

ΔE

ZOOM (again)

$Z=13$

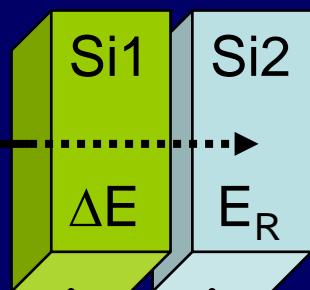


E_R

FAZIA data (LNS)

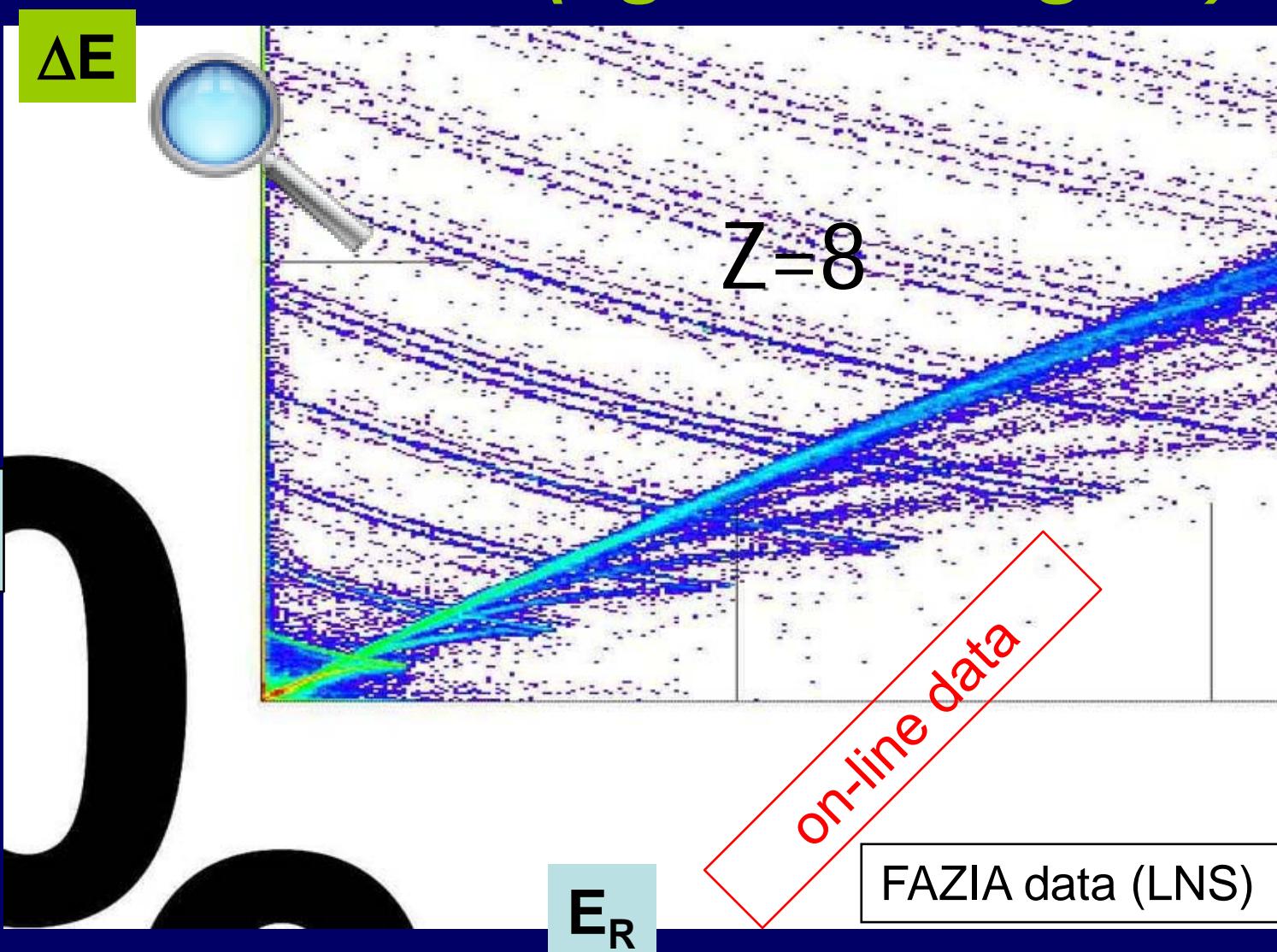
FAZIA PhaseI-R&D

*Usual
 $\Delta E/E$
technique*



100MS/s 14bit
digitizer

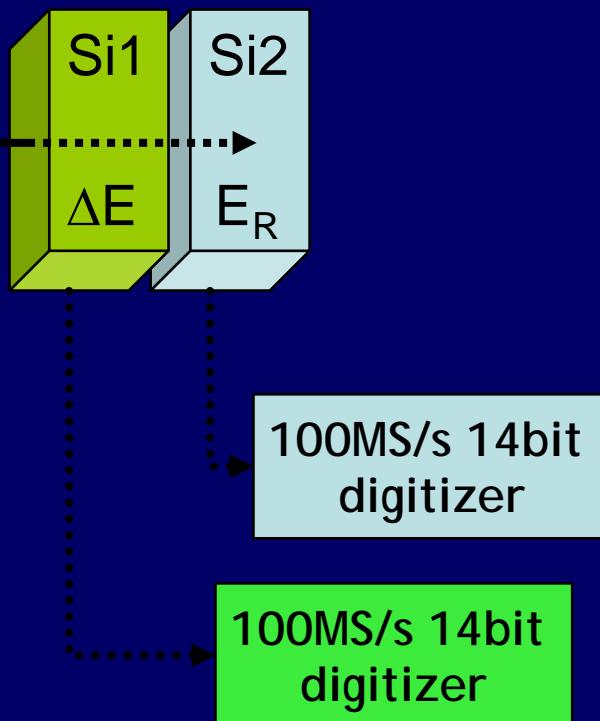
100MS/s 14bit
digitizer



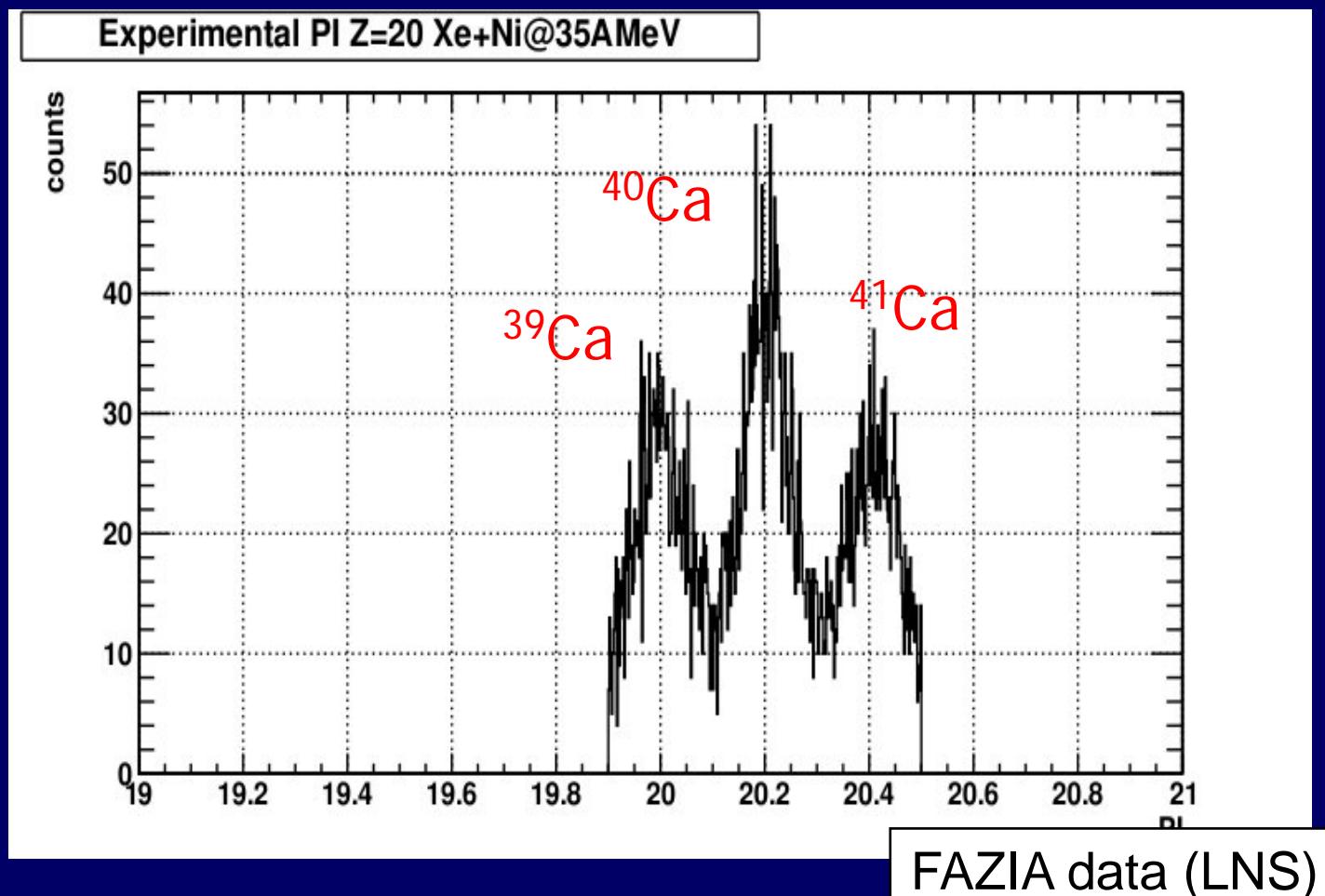
Used configuration:
isotopic identification up to $Z \sim 25$ with $\sim 5\text{GeV}$ full range

FAZIA PhaseI- R&D

*Usual
DE/E
technique*

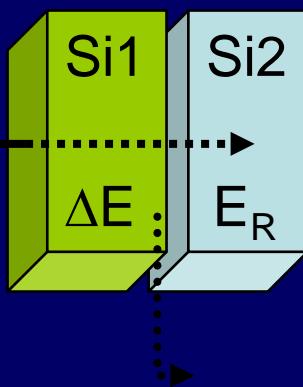


Particle Identification (PID): experimental results obtained by linearizing the three highest intensity Ca isotopes – whole examined Er range (N.Le Neindre, KaliVeda/INDRA program). Unit-mass separation up to $A>40$ (~ 50) is observed.



Used configuration:
isotopic identification up to $Z\sim 25$ with $\sim 5\text{GeV}$ full range

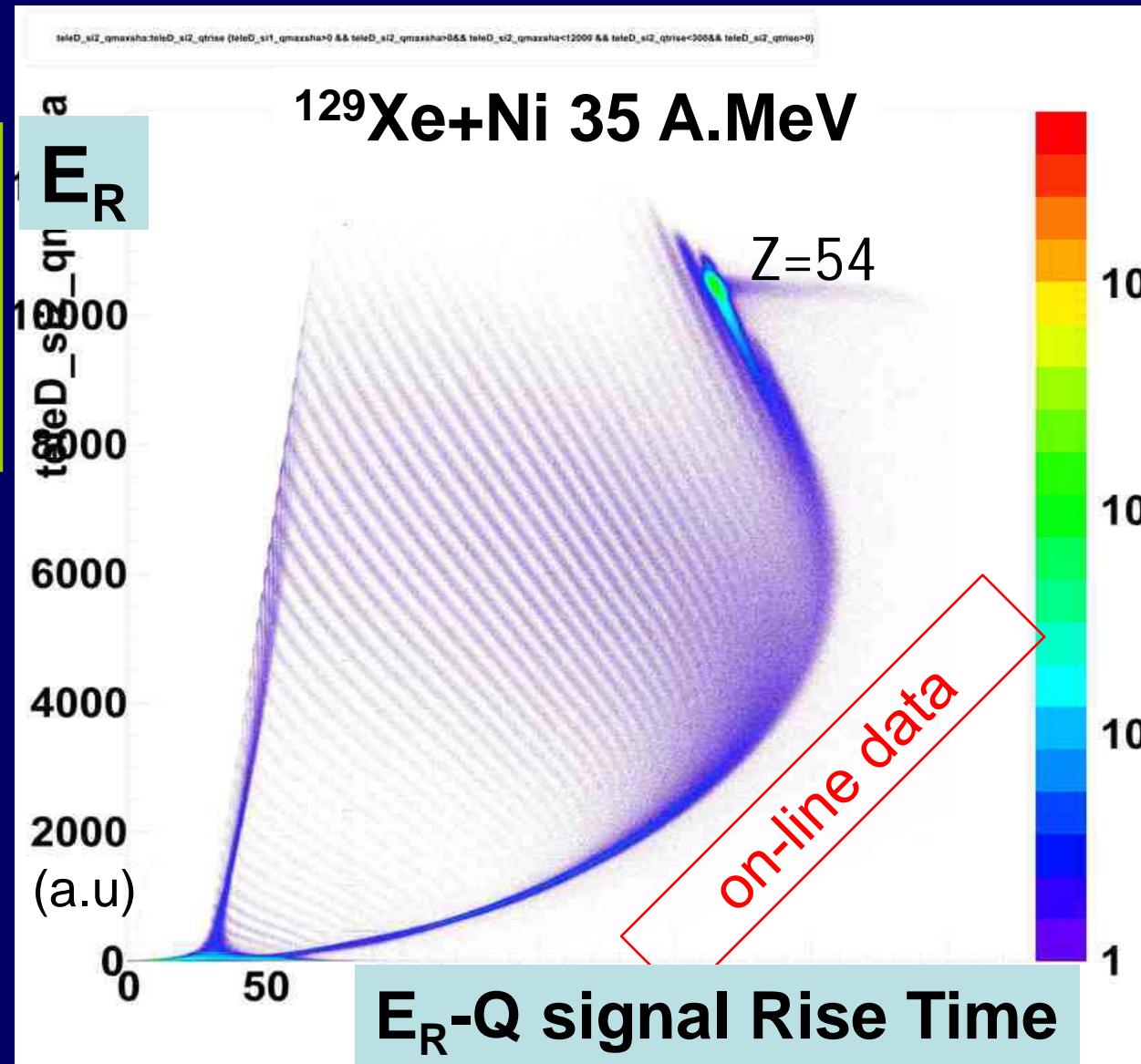
FAZIA PhaseI-R&D



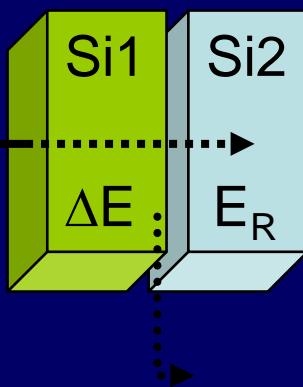
PSA:
*only one
Silicon is
used*

100MS/s 14bit
digitizer

Digital PSA results:
one digitizer,
6 GeV full scale



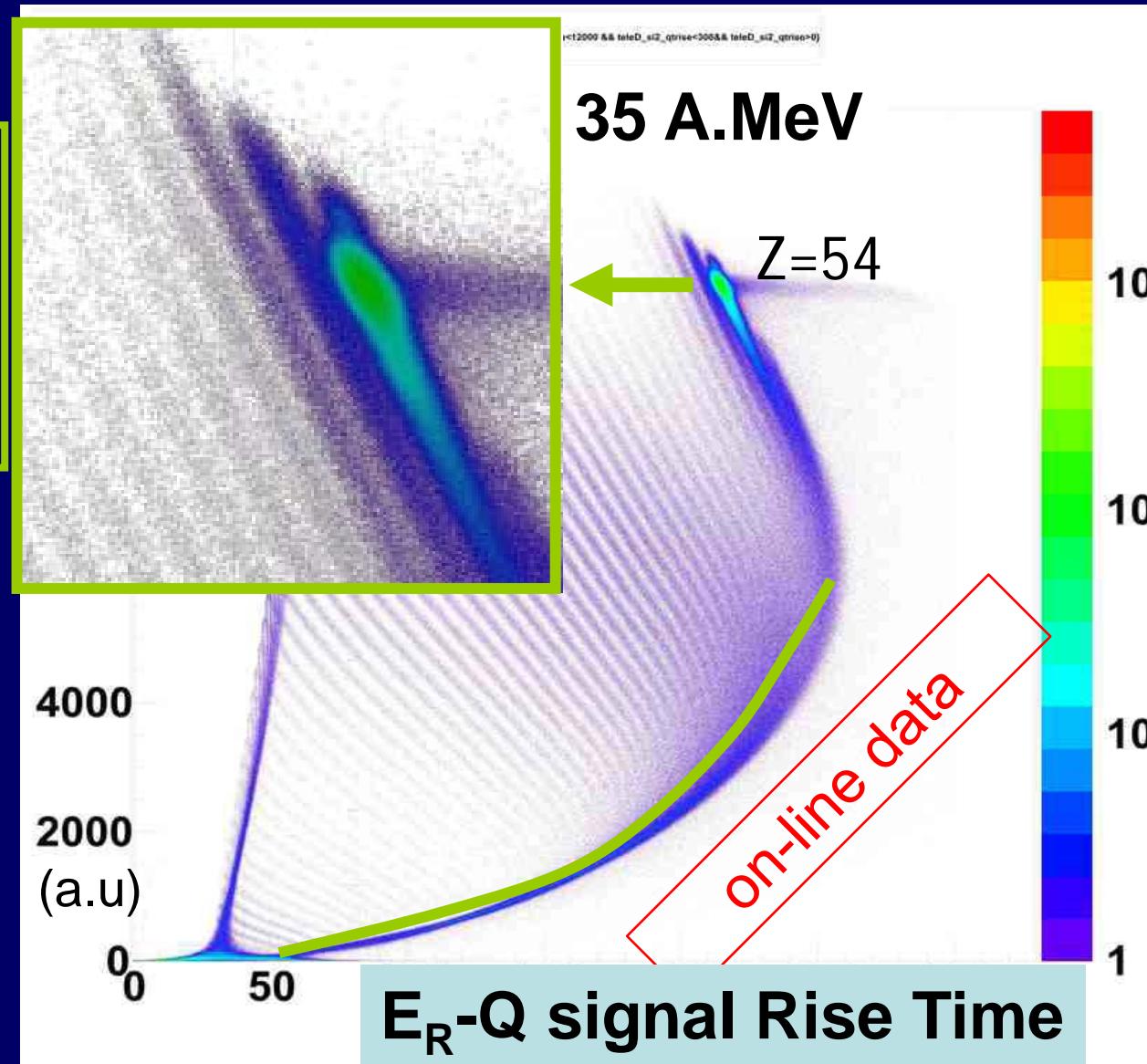
FAZIA PhaseI-R&D



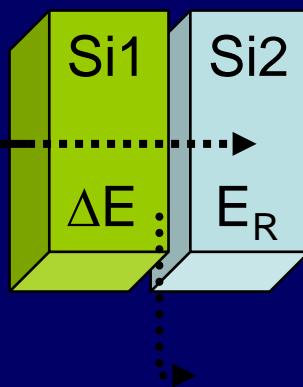
*PSA:
only one
Silicon is
used*

100MS/s 14bit
digitizer

Digital PSA results:
one digitizer,
6 GeV full scale



FAZIA PhaseI-R&D



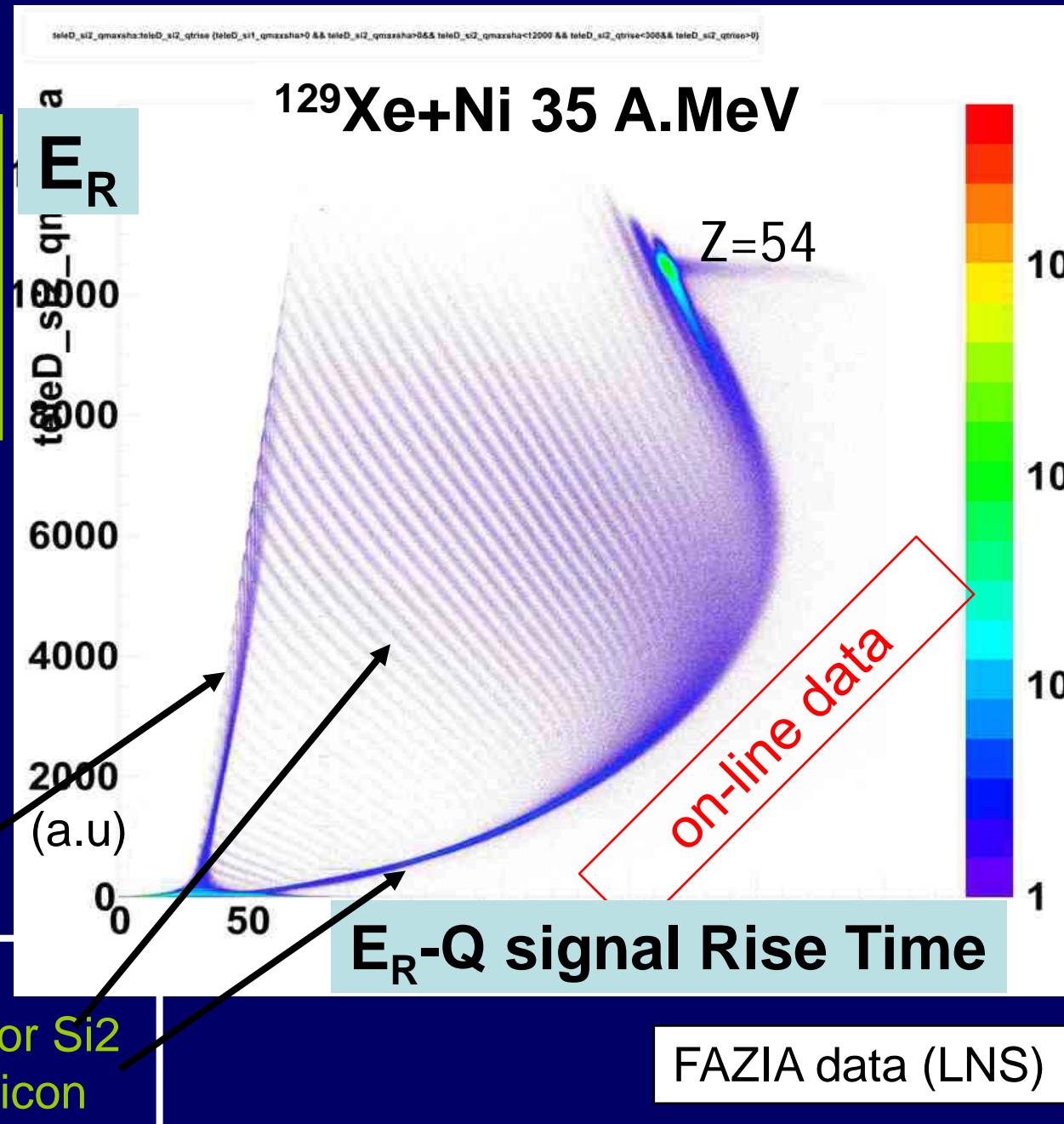
PSA:
*only one
Silicon is
used*

100MS/s 14bit
digitizer

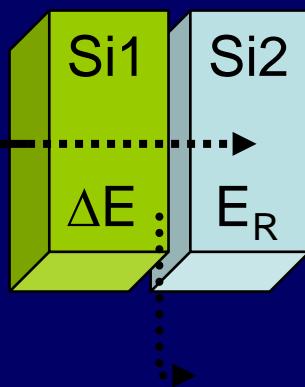
Digital PSA results:
one digitizer,
6 GeV full scale

Punch-through particles.

Particles identified by Silicon detector Si2
Effective threshold: about 30 μm Silicon



FAZIA PhaseI-R&D

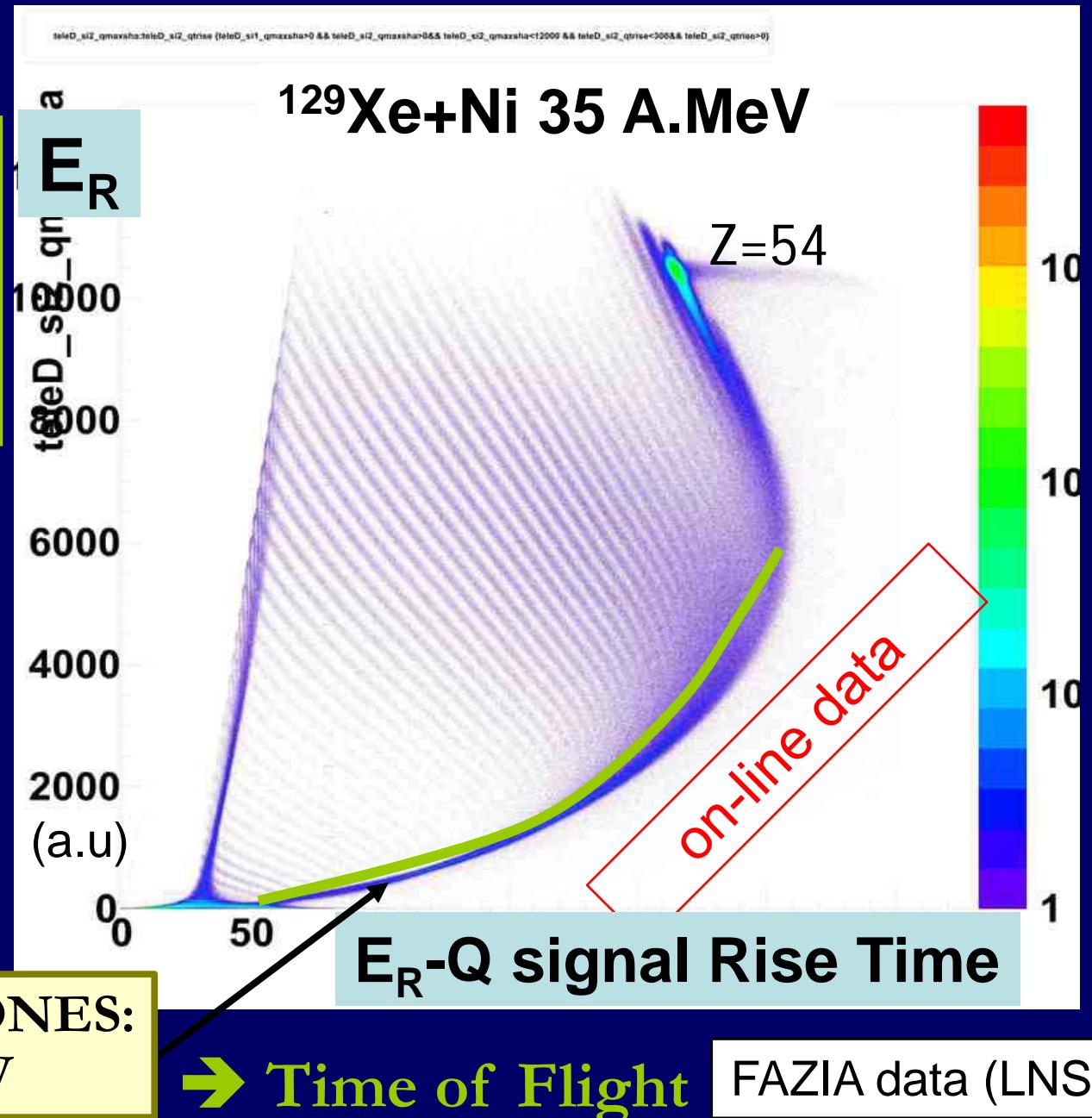


PSA:
*only one
Silicon is
used*

100MS/s 14bit
digitizer

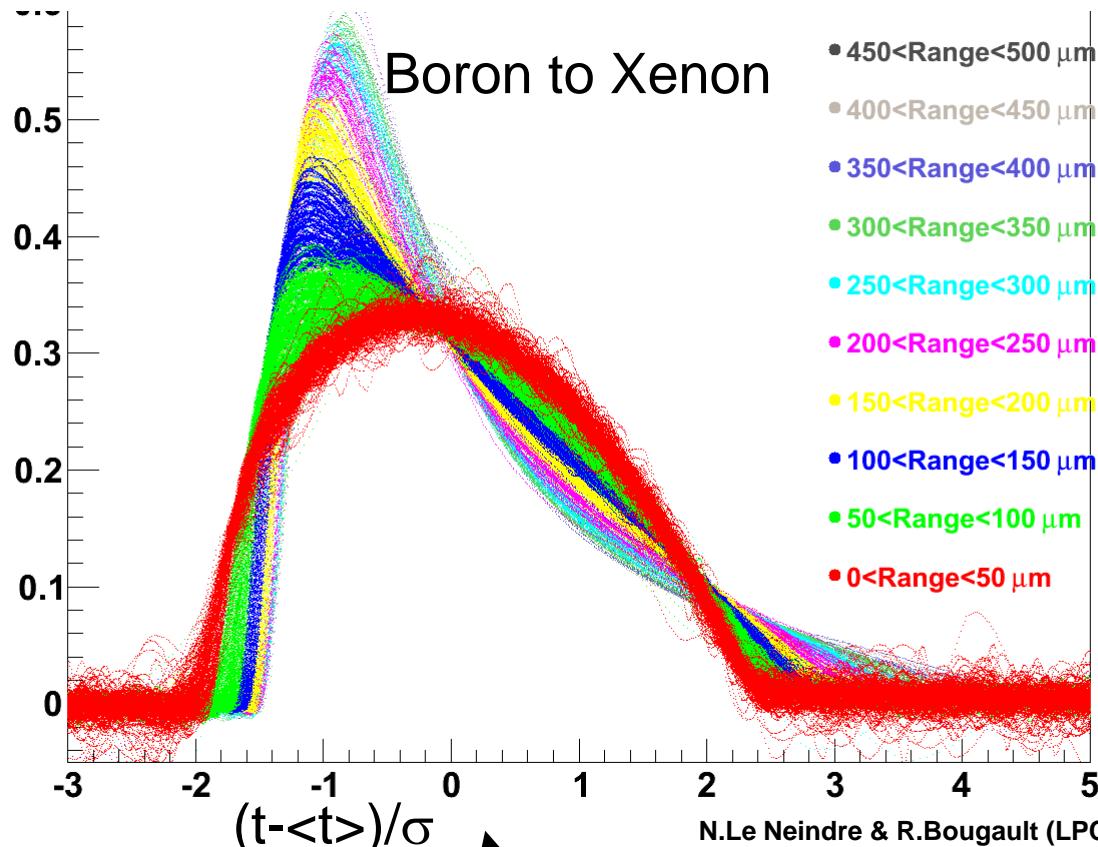
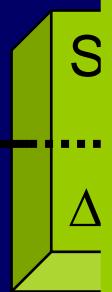
Digital PSA results:
one digitizer,
6 GeV full scale

HIC SUNT LEONES:
below 3-4 A.MeV



FAZIA PhaseI-R&D

SIGNALS "I" CENTRES REDUITS=f(parcours)



Digital FAZIA results.

one digitizer,

6 GeV full scale

HIC SUNT LEONES:
below 3-4 A.MeV

sha<12000 && teleD_si2_qtrise>300&& teleD_si2_qtrise>0

i 35 A.MeV

Z=54

10

10

10

10

1

on-line data

2000
(a.u)

0

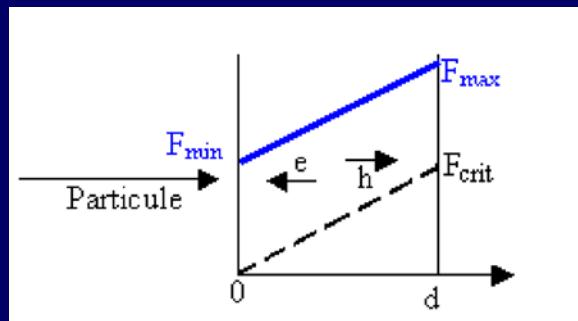
50

E_R -Q signal Rise Time

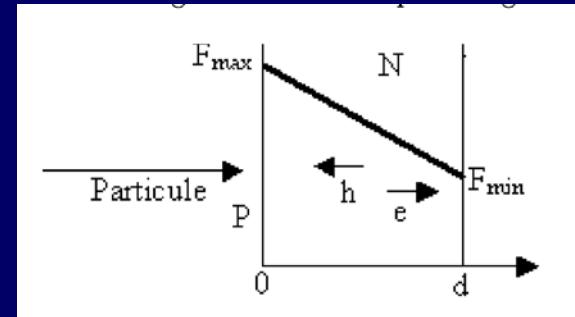
FAZIA data (LNS)

FAZIA PhaseI-R&D

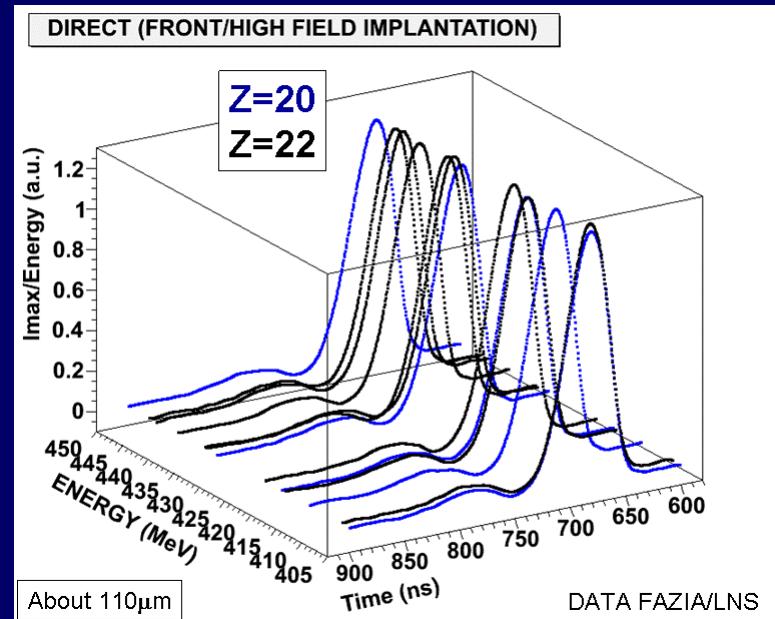
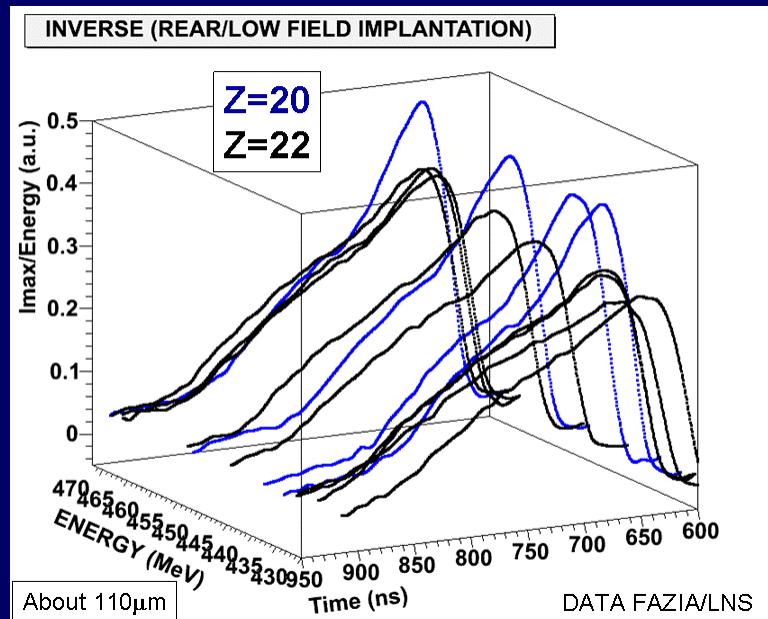
INVERSE (rear)



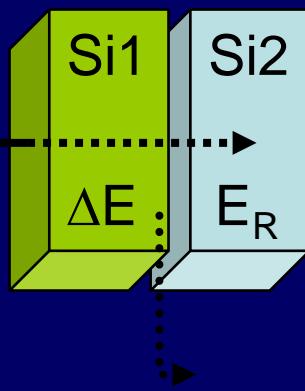
DIRECT (front)



Pulse Shape of stopped particules is different: charge-carrier mobilities of electrons and holes, different plasma-erosion times



FAZIA PhaseI-R&D

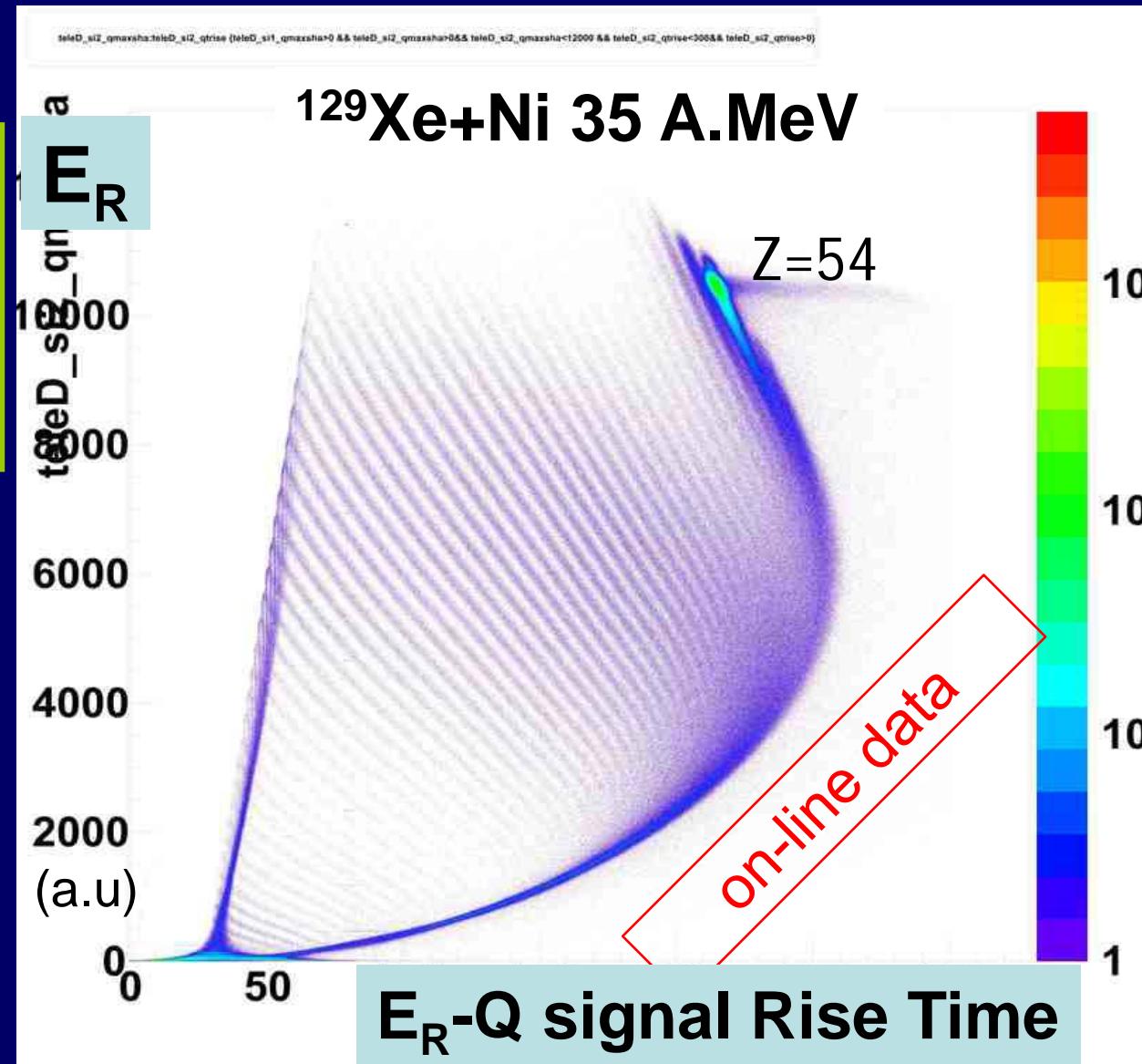


PSA:
*only one
Silicon is
used*

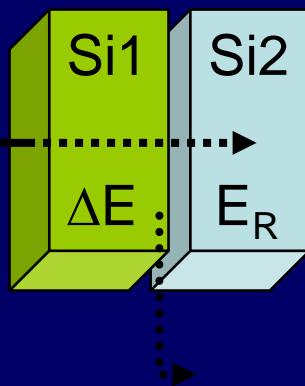
100MS/s 14bit
digitizer

Digital PSA results:
one digitizer,
6 GeV full scale

FAZIA data (LNS)

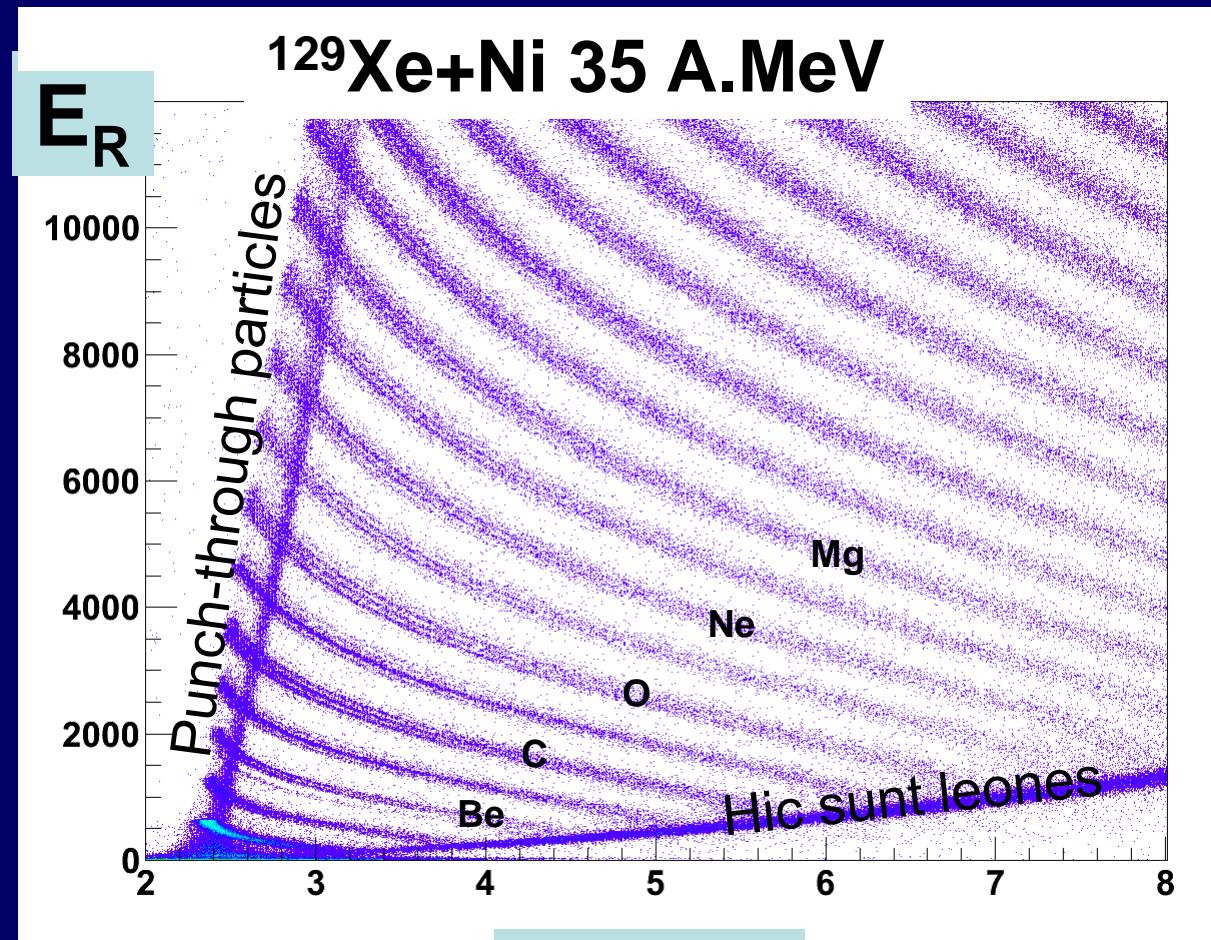


FAZIA PhaseI- R&D



*PSA:
only one
Silicon is
used*

Digital PSA results:
one digitizer,
0.7 GeV full scale



QUESTION OF 2 GAINS:

- 6GeV full scale → Z Id.
- 0.7 GeV full scale → Z and A Id.

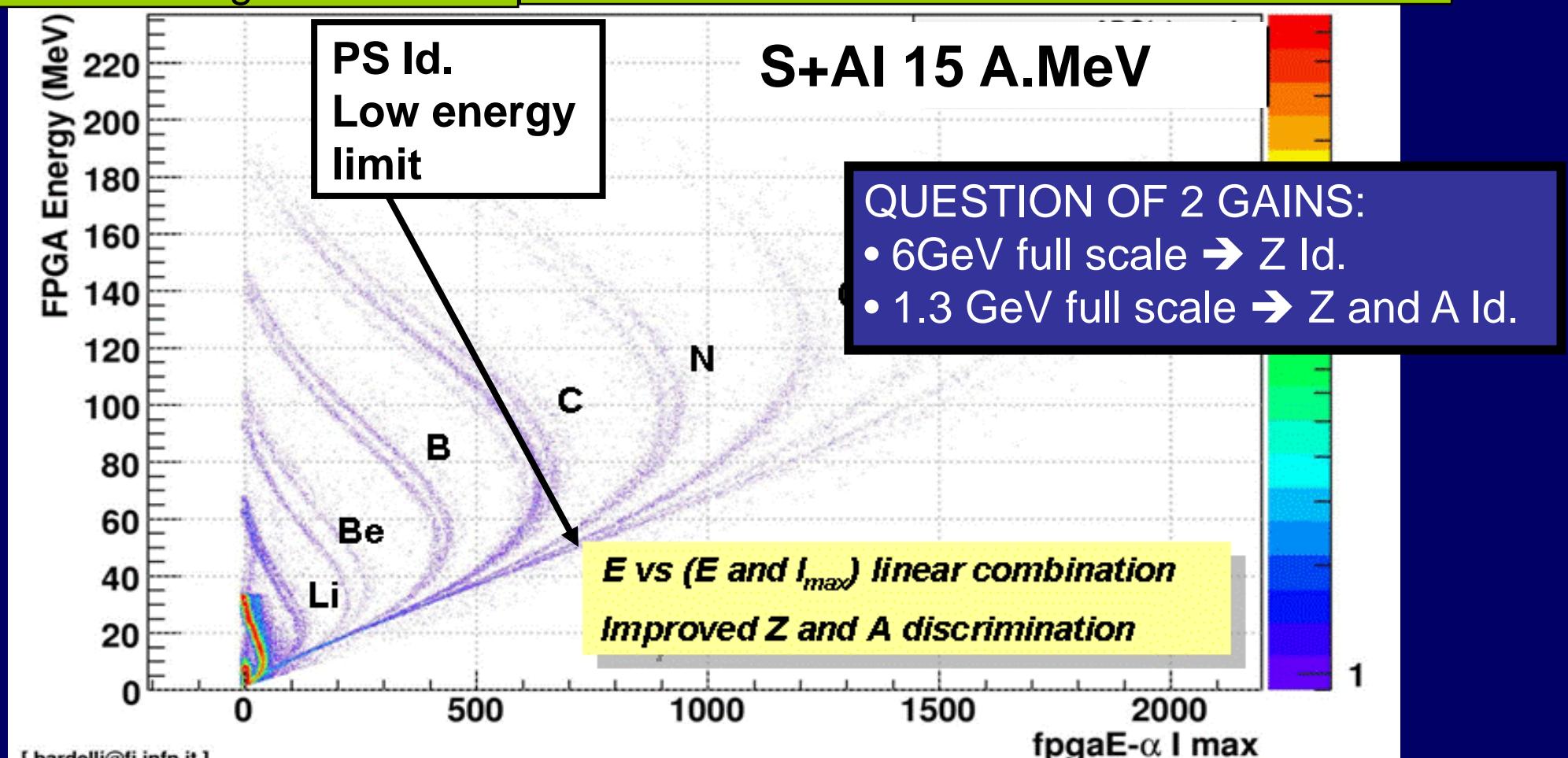
E_R/I_{\max}

FAZIA data (GANIL2010)

FAZIA PhaseI- R&D

CHARGE (14bits, 100MS/s)
CURRENT (12bits, 125MS/s)
1.3 GeV full range

IONS IDENTIFIED BY ONE DETECTOR



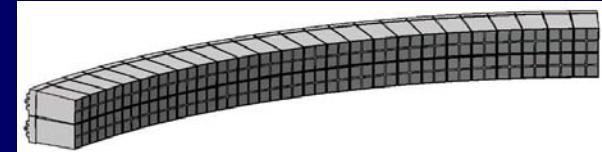
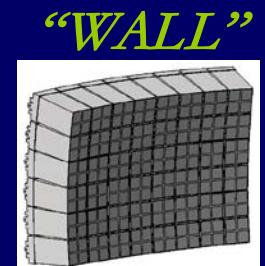
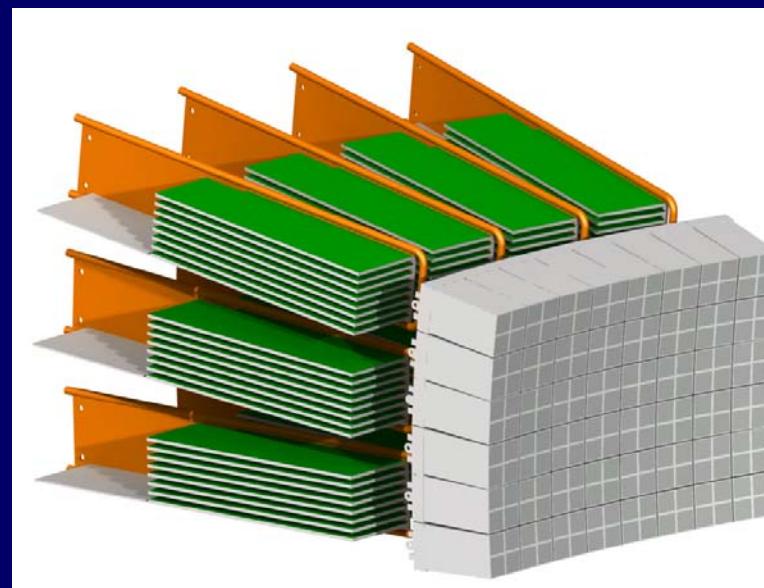
FAZIA demonstrator

FAZIA PHASE2 “demonstrator & physics” :

- Built (2011-2013) a demonstrator of 192 telescopes Si/Si/CsI with “all” the finals (4 π detector) electronics, mechanical solutions.
- With this demonstrator coupled to existing multi-detectors (INDRA, GARFIELD, CHIMERA,...), realize experiments (GANIL, SPIRAL2, LNL/SPES, LNS).

12 BLOCKS
48 MODULES
192 TELESCOPES Si/Si/CsI

- Telescope	
Si(300 μ)	- charge 250 MeV f.s. 250 Ms/s 14 bit
	- charge 4 GeV f.s 100 Ms/s 14 bit
	- current 250 Ms/s 14 bit
Si(500 μ)	- charge 4 GeV f.s 100 Ms/s 14 bit
	- current 250 Ms/s 14 bit
CsI(phdiode)	- charge 4 GeV f.s 100 Ms/s 14 bit

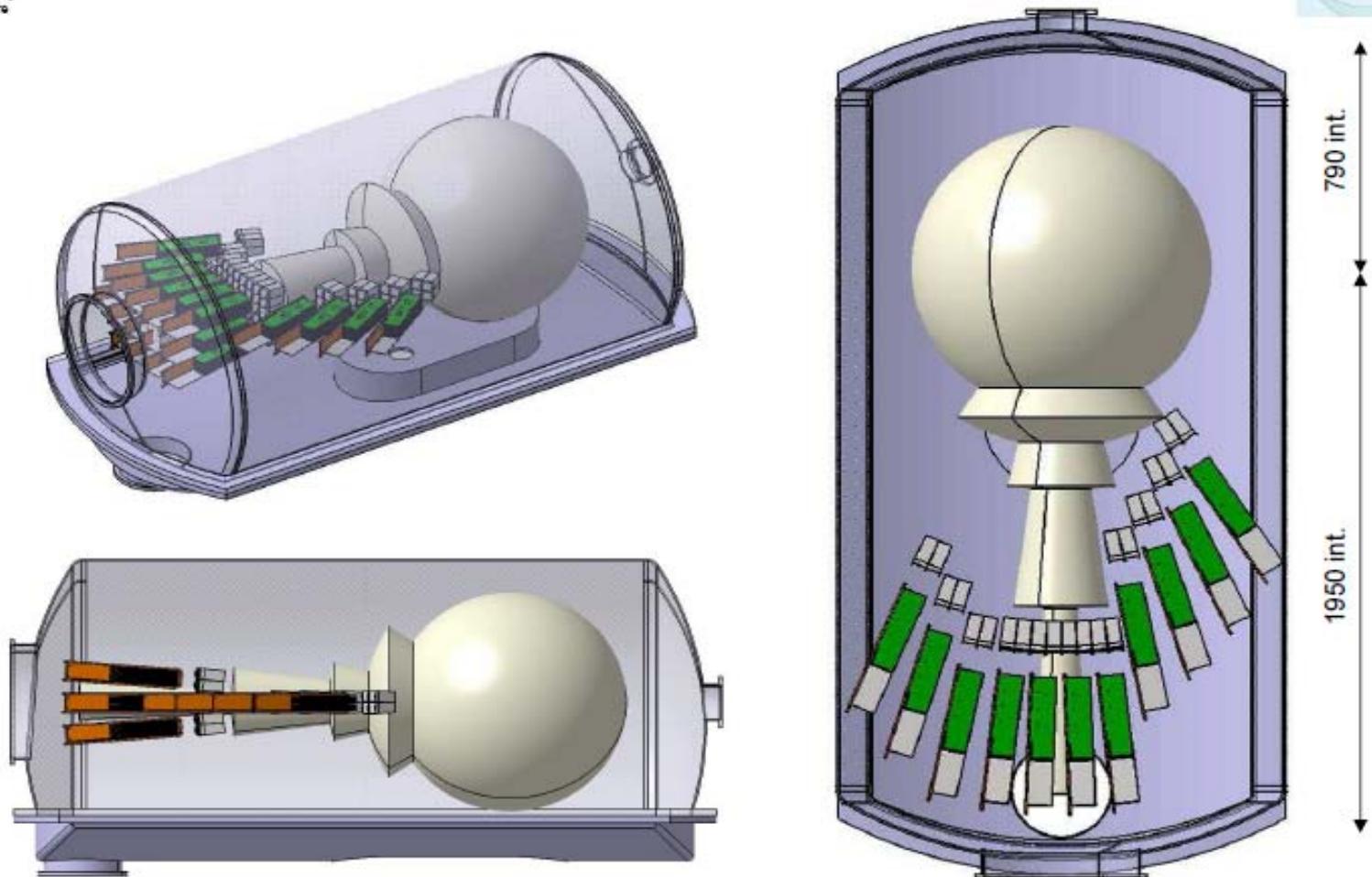


FAZIA Phase2



Laboratoire de Physique
Corpusculaire

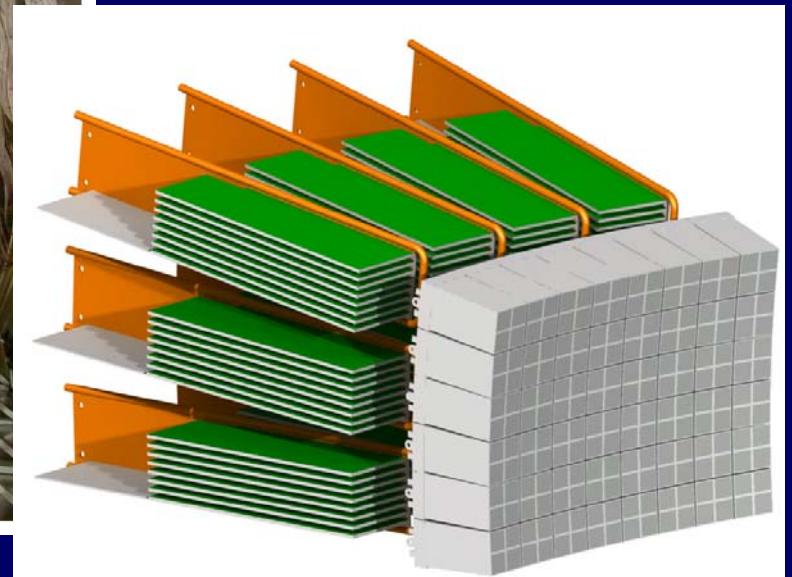
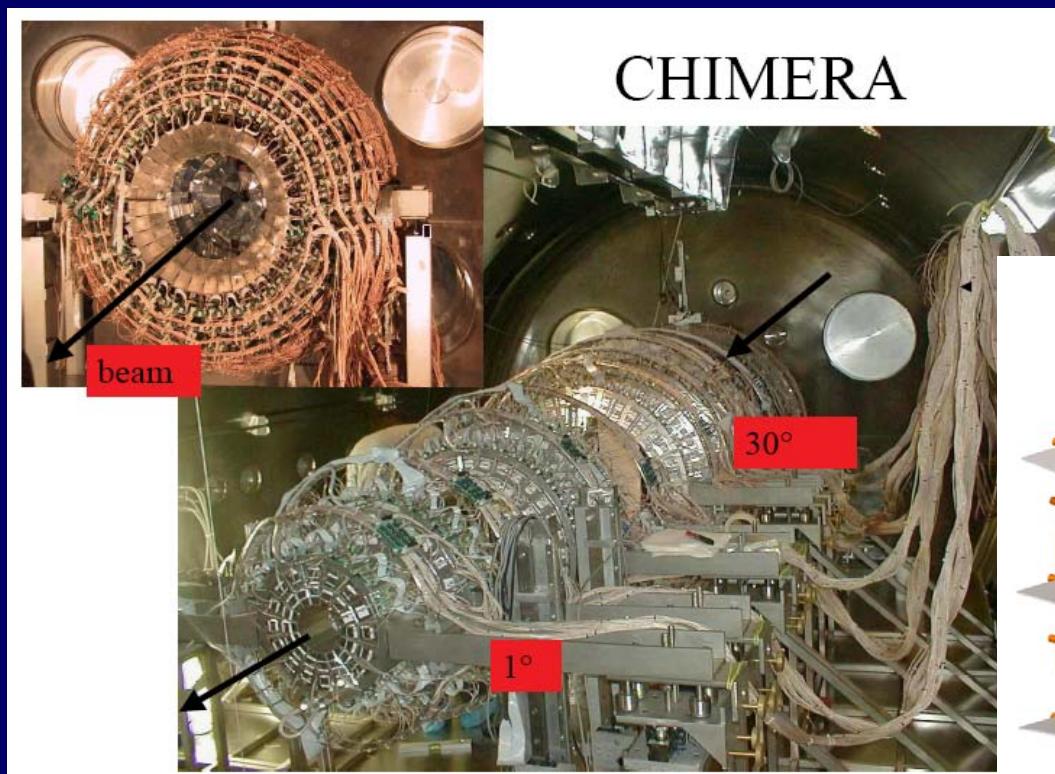
FAZIA – INDRA



Bloc : R600 à R1200 & Wall : R1200

FAZIA Phase2

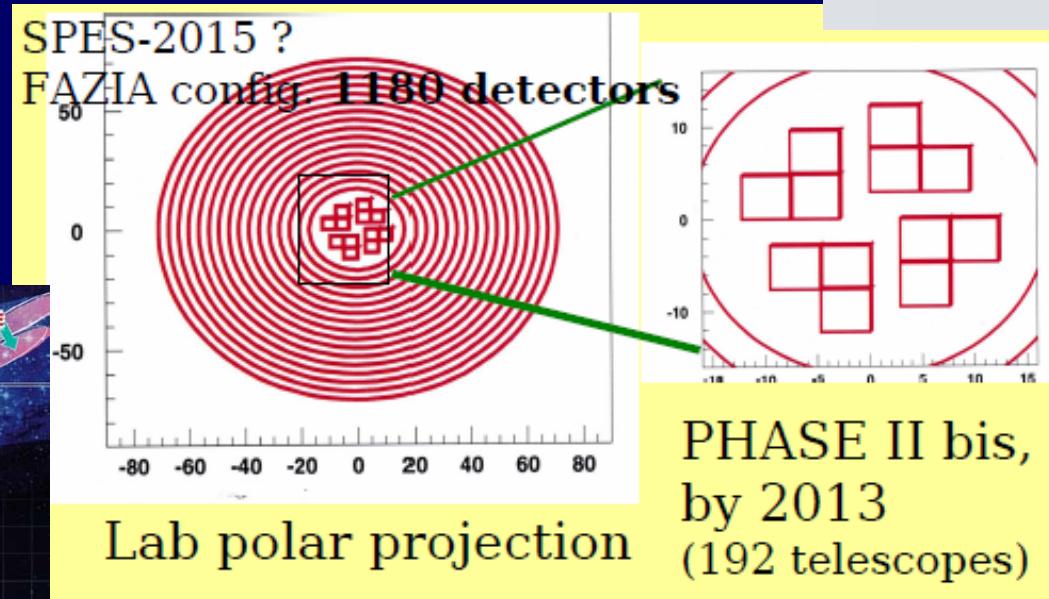
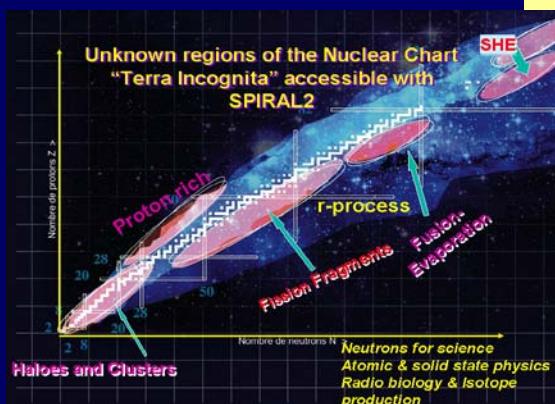
FAZIA@CHIMERA



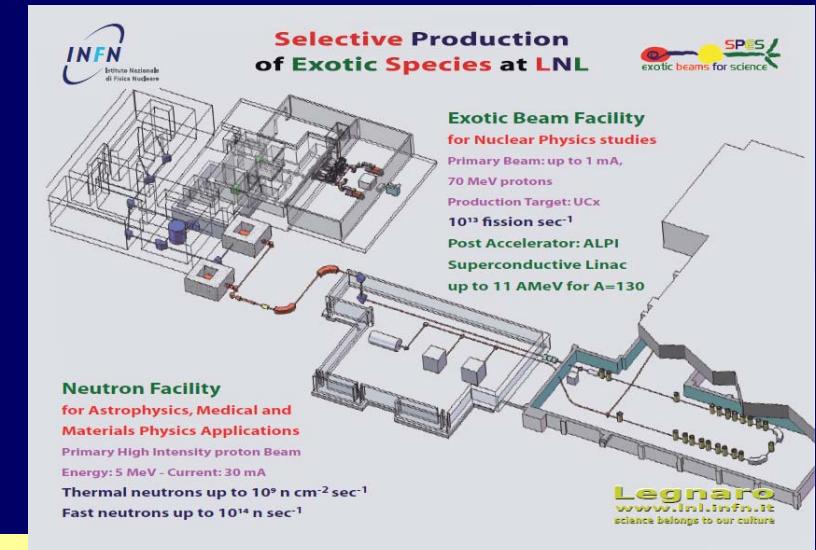
FAZIA Phase2

FAZIA@GARFIELD

... and FUTURE:



(G.Casini et al. SPES-WS)



FAZIA Phase2 2011-2013

TECHNICAL CHOICE :

Digitize as close as possible /preamplifier

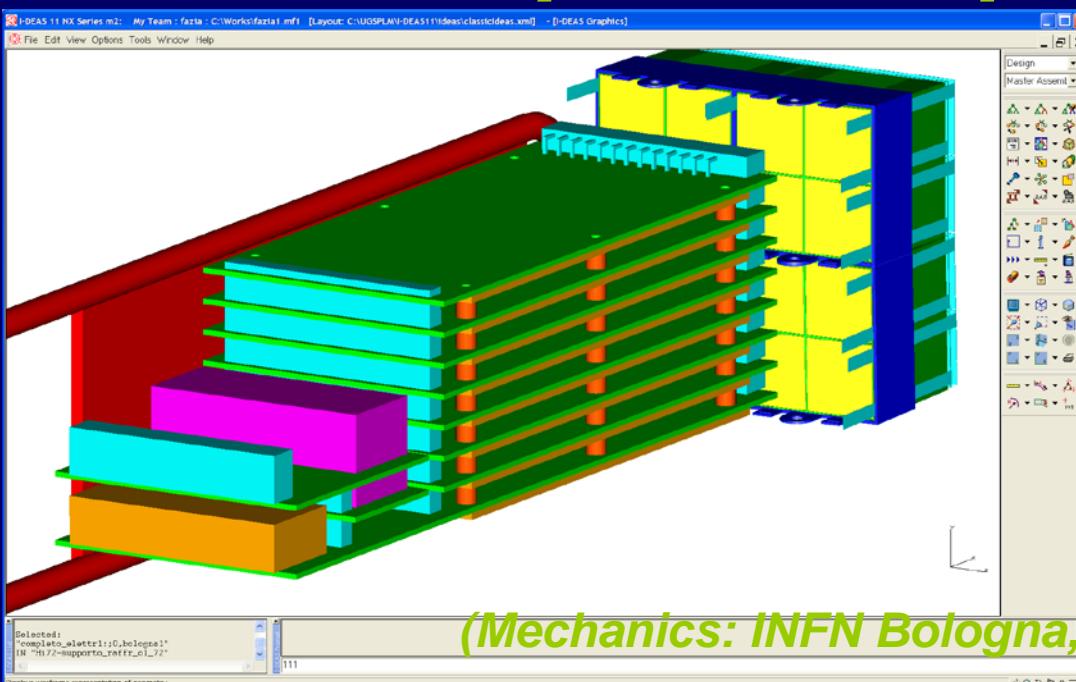
- Noise reduction
- Avoid signal distortion (PSA)
- Simplify signal transmission (high number of channels)

- Telescope			
Si(300μ)	- charge	250 MeV f.s.	250 Ms/s 14 bit
	- charge	4 GeV f.s	100 Ms/s 14 bit
	- current		250 Ms/s 14 bit
Si(500μ)	- charge	4 GeV f.s	100 Ms/s 14 bit
	- current		250 Ms/s 14 bit
CsI(phdiode)	- charge	4 GeV f.s	100 Ms/s 14 bit

2 gains for the first Silicium detector

FAZIA Phase2 2011-2013

TECHNICAL CHOICE :
Digitize as close as possible /preamplifier

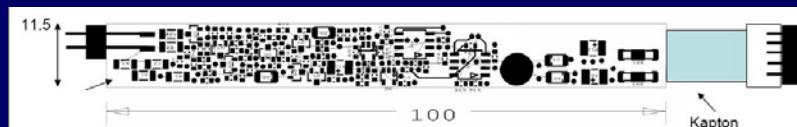


- 16 telescope “Block” structure
- 8 analog./dig. cards
- with mother board (communication , HV and “low bias”)
- 1 optic fibber per “Block” (3Gbit/s)

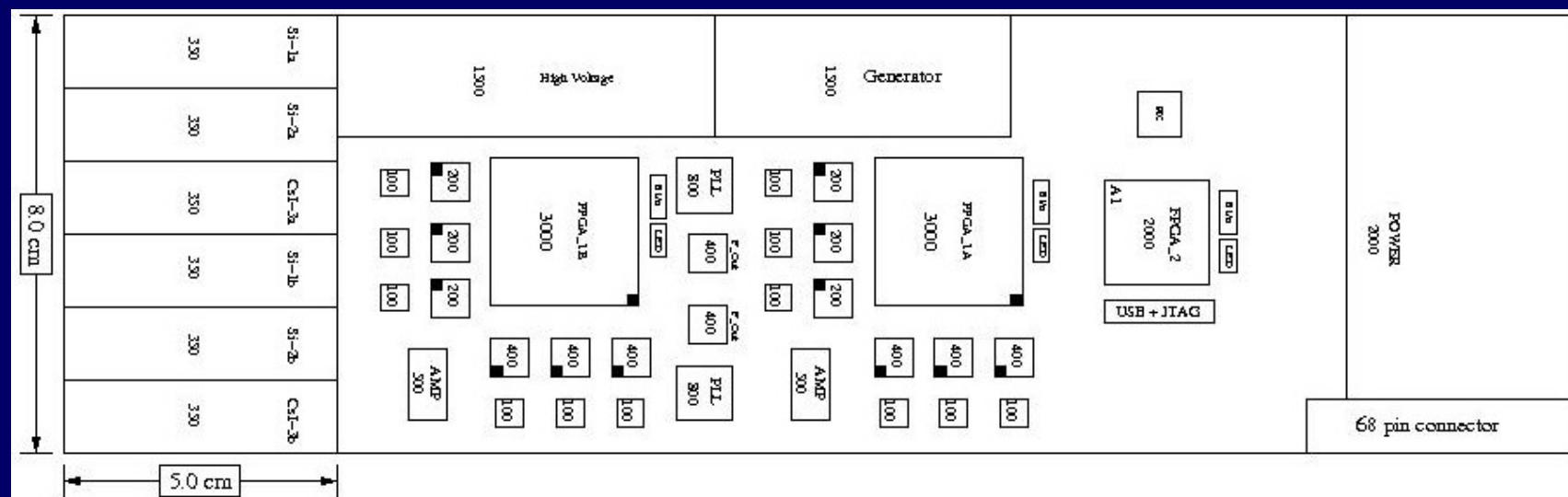
FAZIA Phase2 2011-2013

TECHNICAL CHOICE : *Digitize as close as possible /preamplifier*

PACI preamp.
Charge & Current



(P.Edelbruck IPNOrsay)



(Card for 2 telescopes)

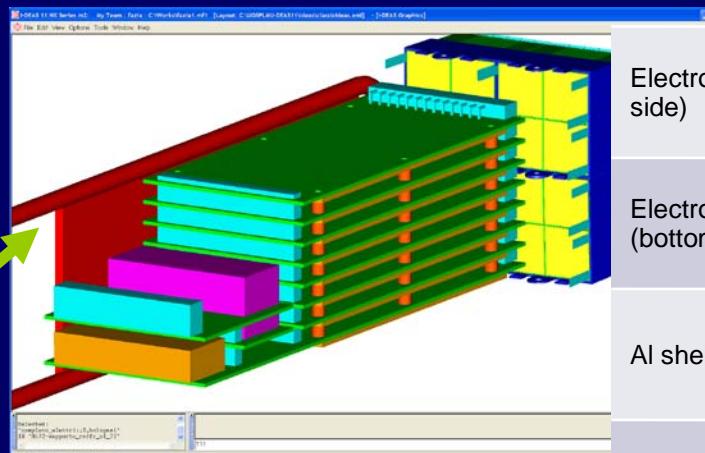
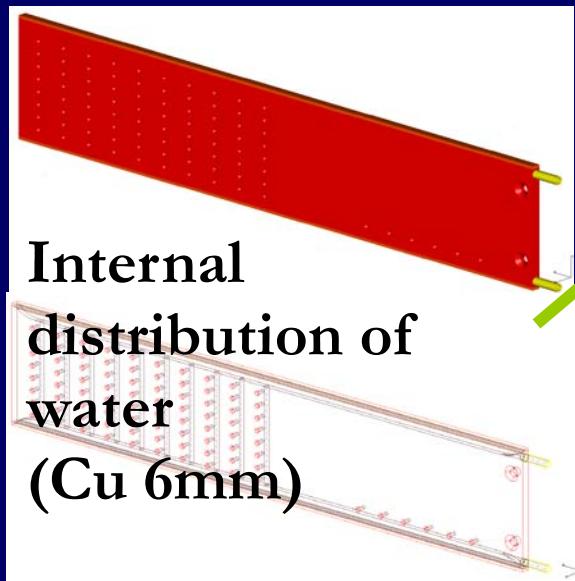
(IPNOrsay, INFN Napoli)

“Price to pay”

- 25 Watts per card
- Cooling system

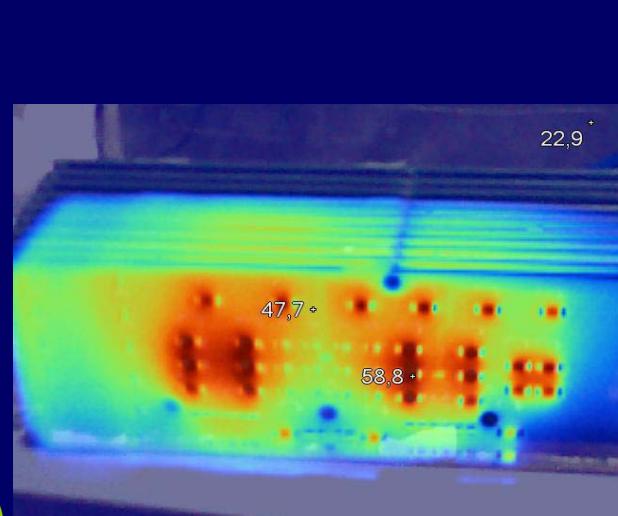
FAZIA Phase2 2011-2013

TECHNICAL CHOICE : *Digitize as close as possible /preamplifier*



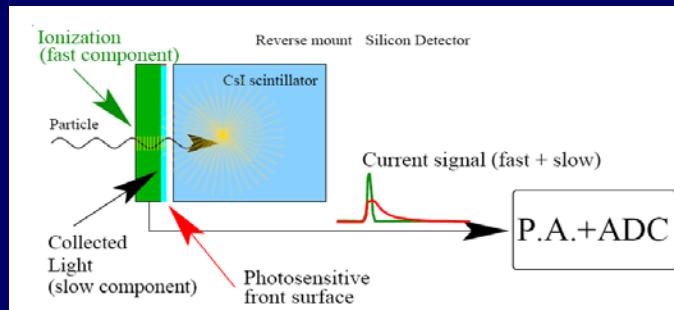
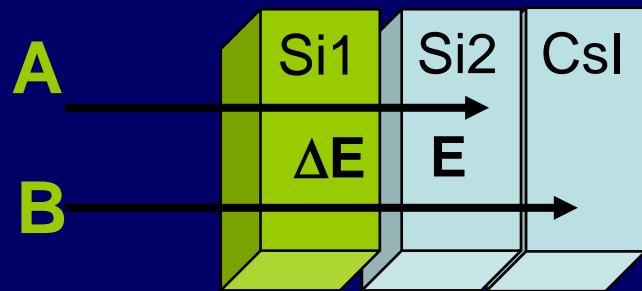
Air test : Existence
Of hot points
(improve)

(INFN Napoli)



Electronic card temperature (top side)	50 °C	45 °C
Electronic card temperature (bottom side)	43 °C	40 °C
Al shelf temperature	35 °C	32 °C
Cu plate temperature	34 °C	28 °C
TESTS under vaccum		
Outgoing water temperature	25 °C	20,1 °C
Incoming water temperature	20 °C	17,5 °C
Cooling water flow	0,5 l/m	1 l/m

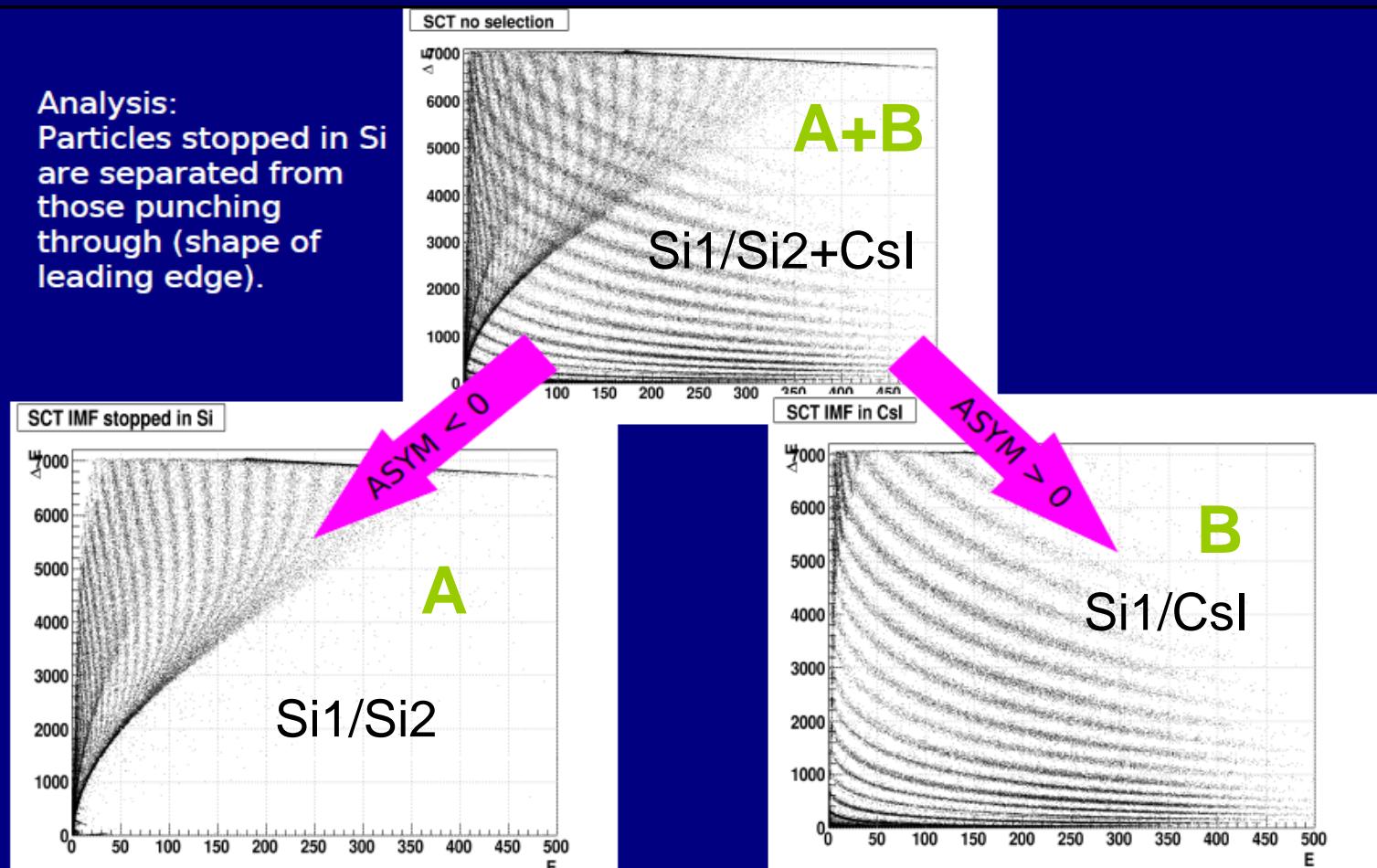
FAZIA



Single Chip Telescope: no photodiode

Separation
algorithm using
 ΔE and T_{rise}

Analysis:
Particles stopped in Si
are separated from
those punching through
(shape of
leading edge).

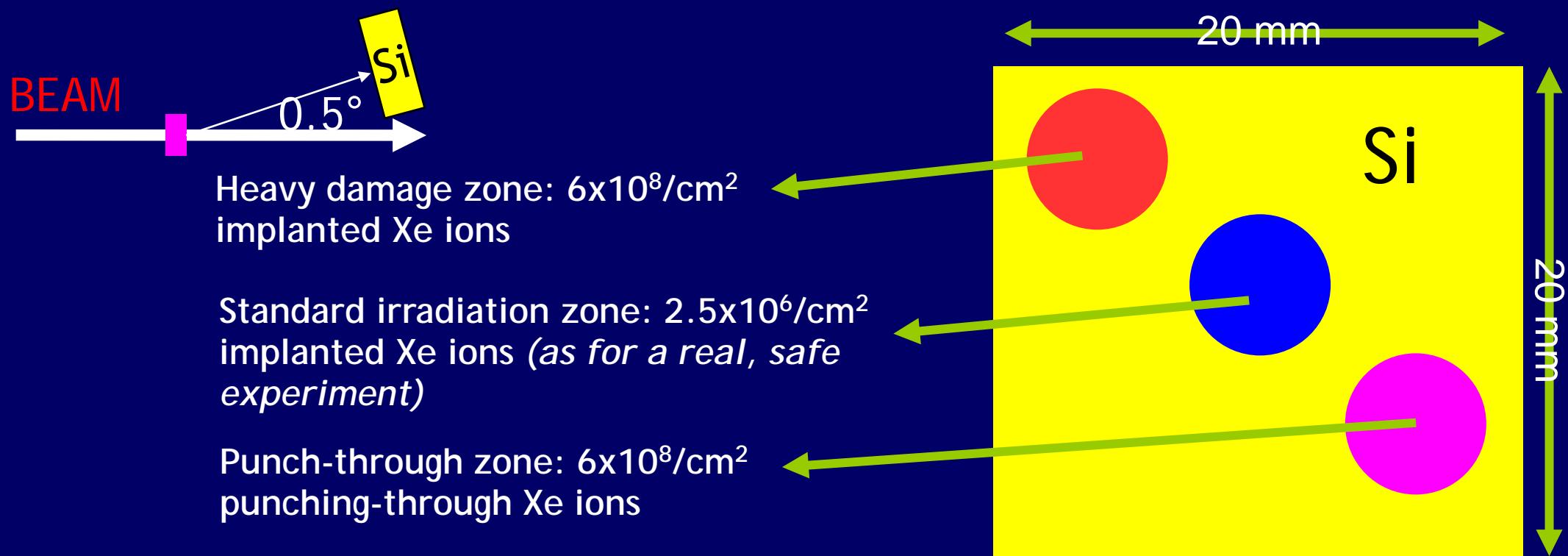


FAZIA data (LNS)
Analysis: Firenze

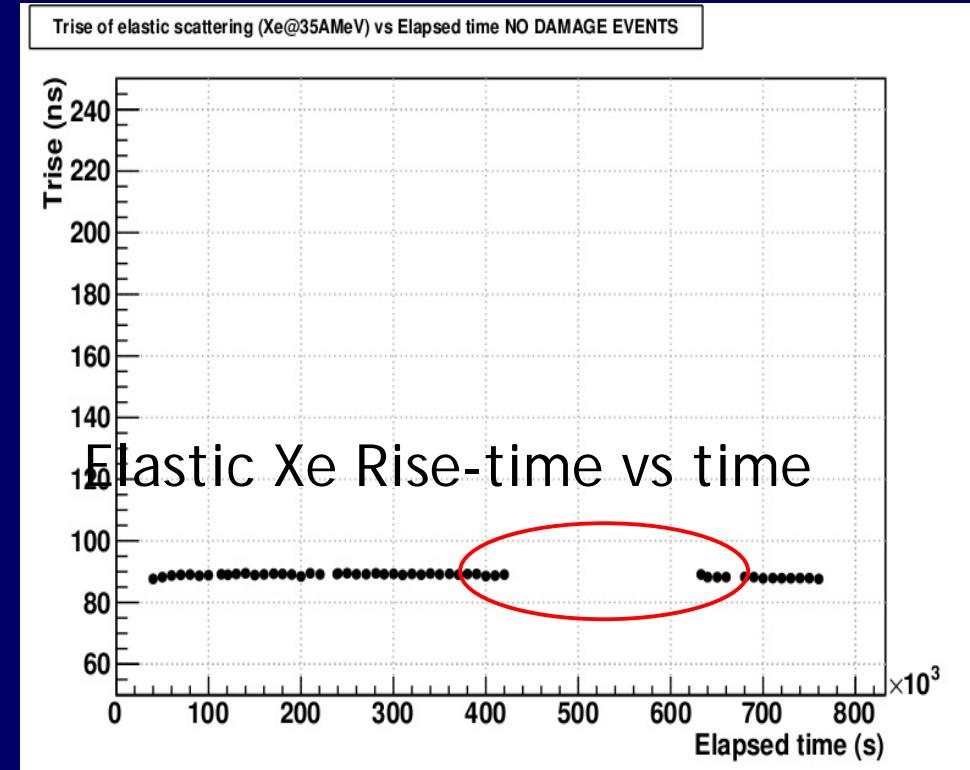
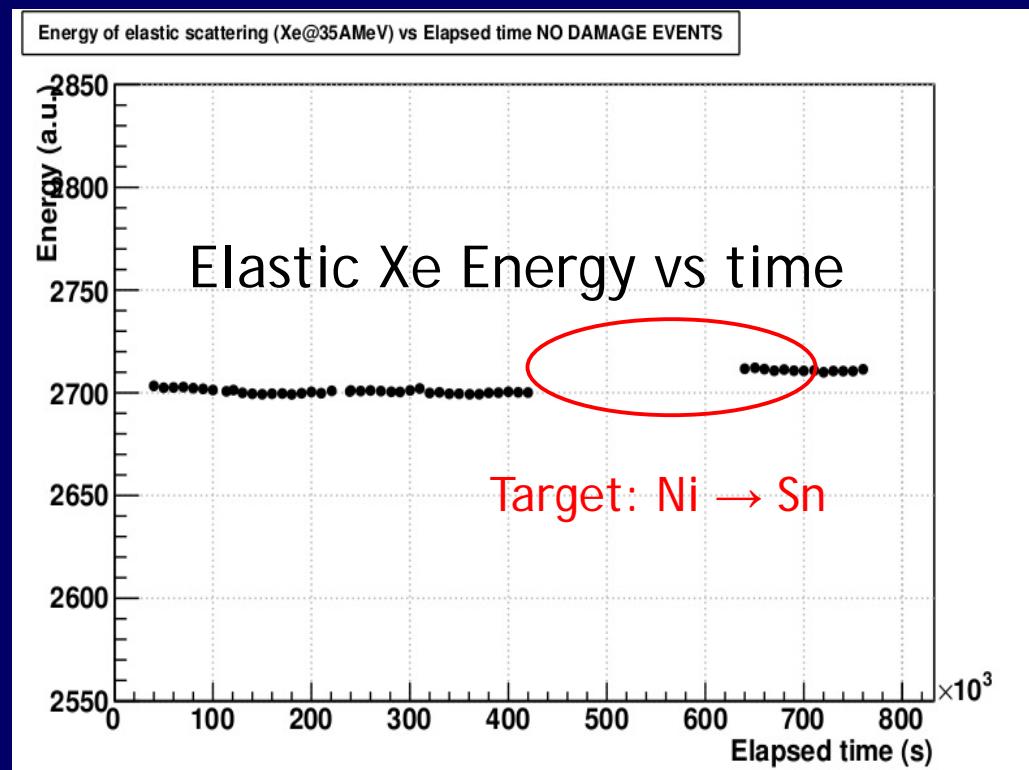
FAZIA: RADIATION DAMAGE

LNS (November 2009): “Radiation damage and PSA”

- A $300\mu\text{m}$ detector was placed at very forward angles
 - Mono-energetic (elastically scattered) Xe ions of 35 MeV/n are either implanted or punching-through, depending of absorbers, in narrow zones of the same Silicon detector
 - The detector was periodically irradiated and tested, in terms of energy and risetime resolution, by moving it far from the high flux region. Only elastically scattered Xe ions are measured (*worst case*)
 - A total fluence of $1.2 \times 10^9 \text{ ions/cm}^2$ has been experienced by the detector

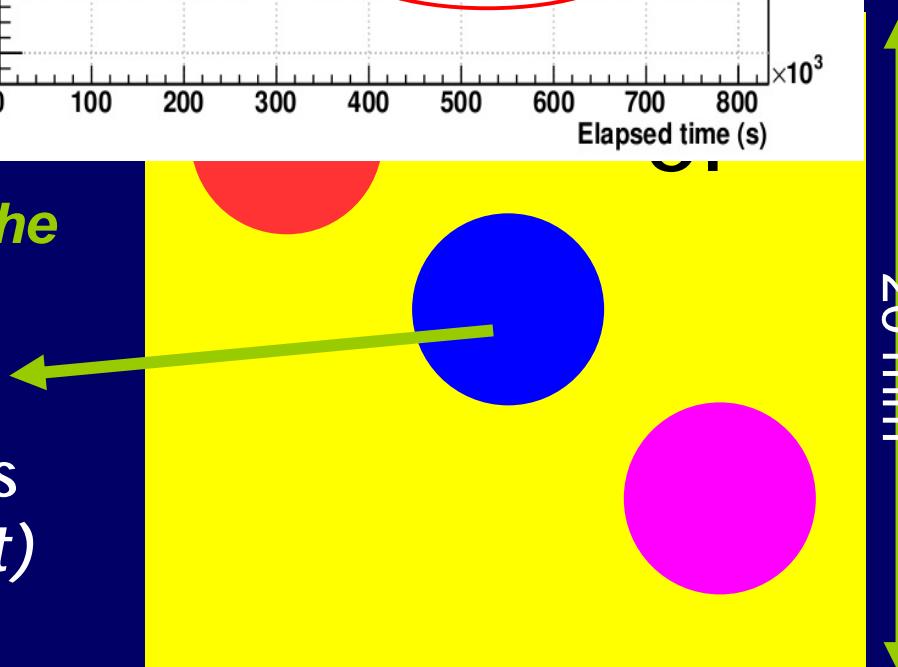


FAZIA: RADIATION DAMAGE

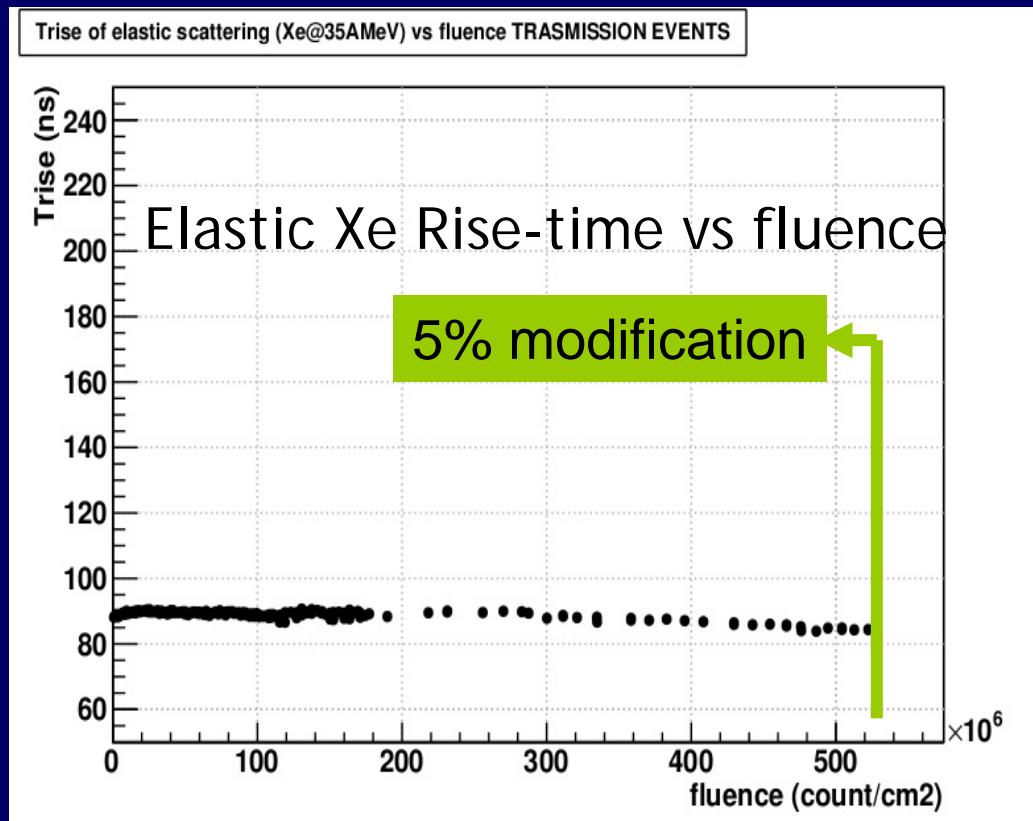
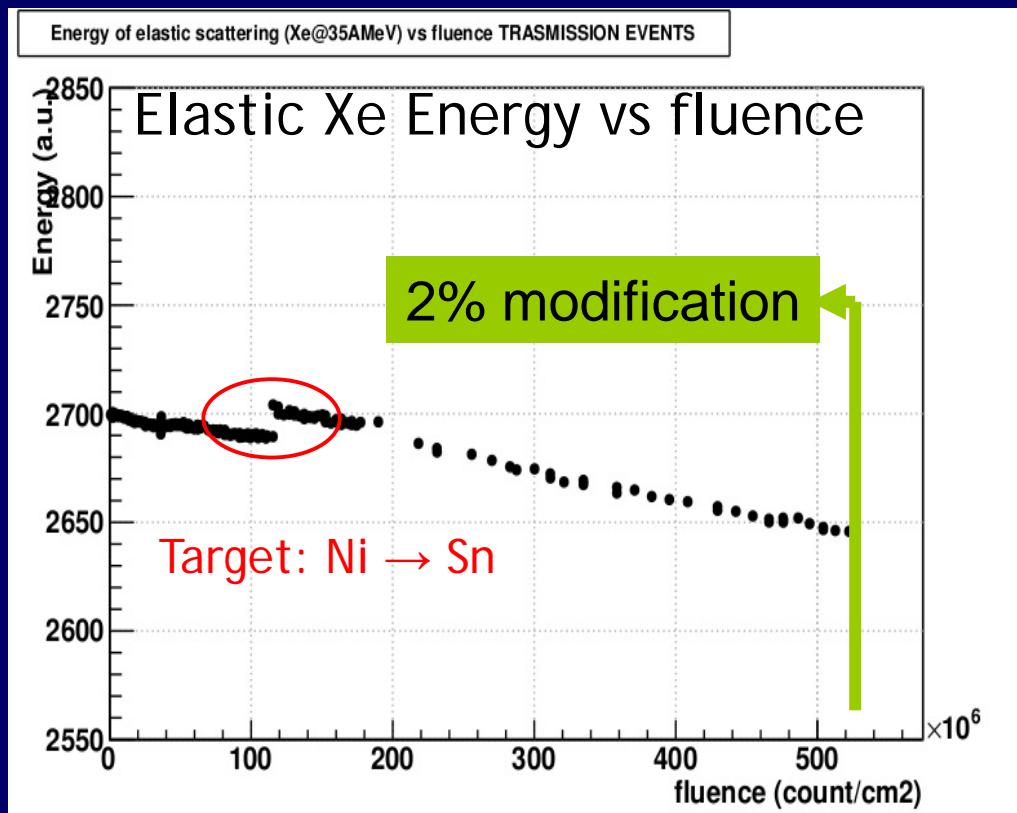


Keeping the field constant by changing the bias Voltage

Standard irradiation zone:
 $2.5 \times 10^6 / \text{cm}^2$ implanted Xe ions
(as for a real, safe experiment)

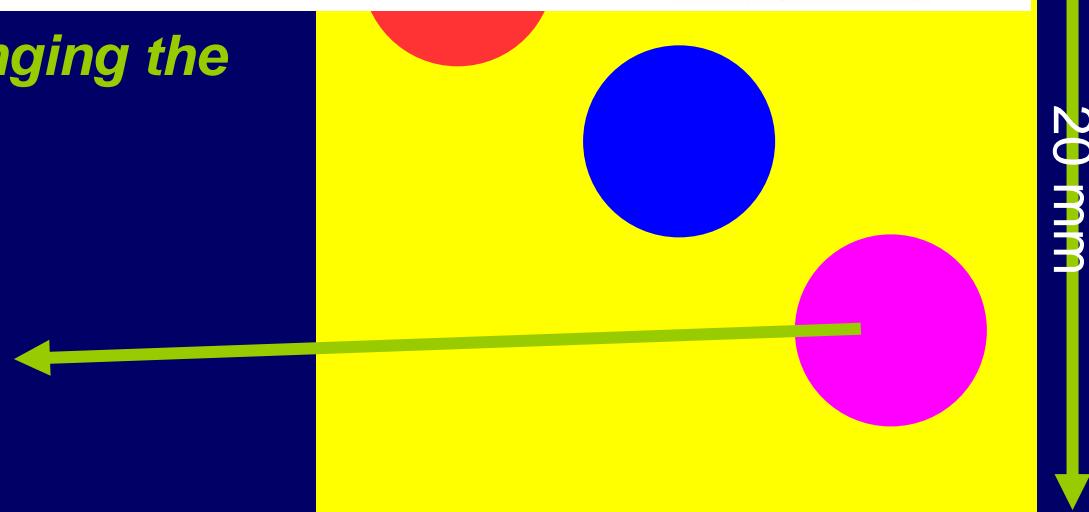


FAZIA: RADIATION DAMAGE



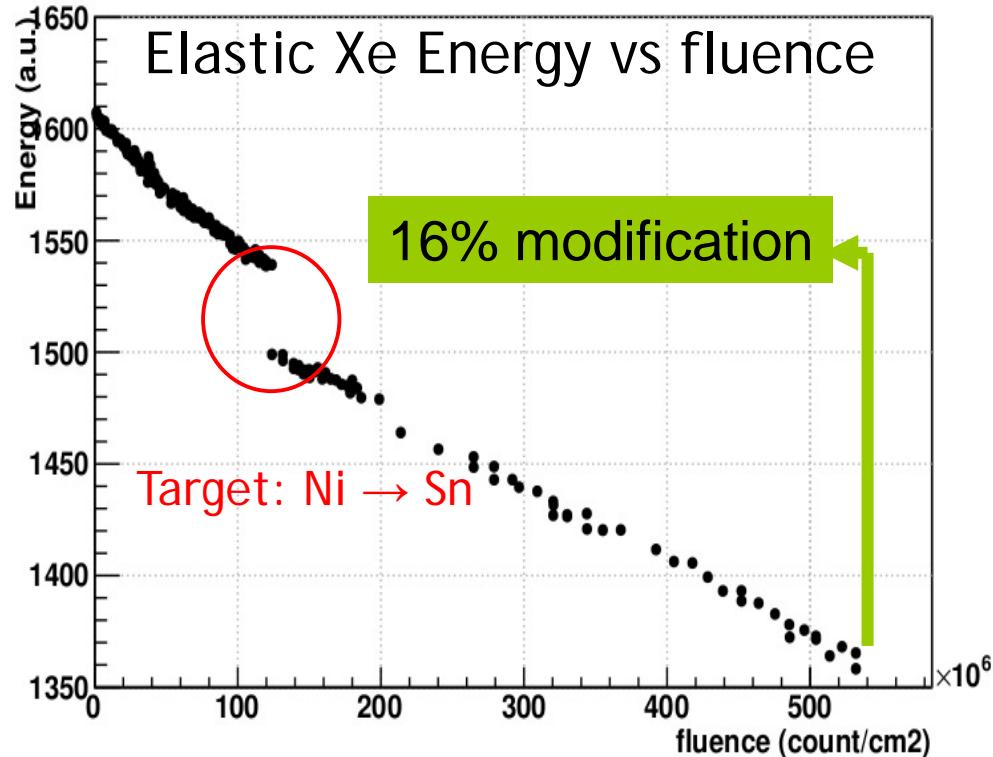
Keeping the field constant by changing the bias Voltage

Punch-through zone:
 $6 \times 10^8 / \text{cm}^2$ punching-through Xe ions

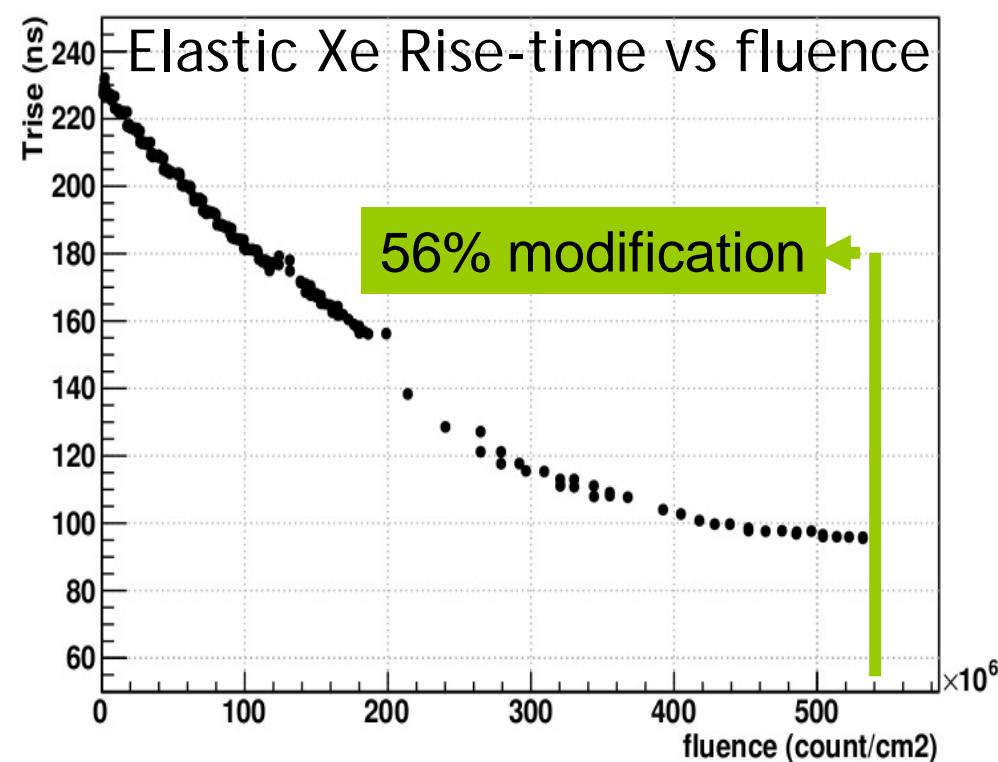


FAZIA: RADIATION DAMAGE

Energy of elastic scattering (Xe@35AMeV) vs fluence STOPPED EVENTS

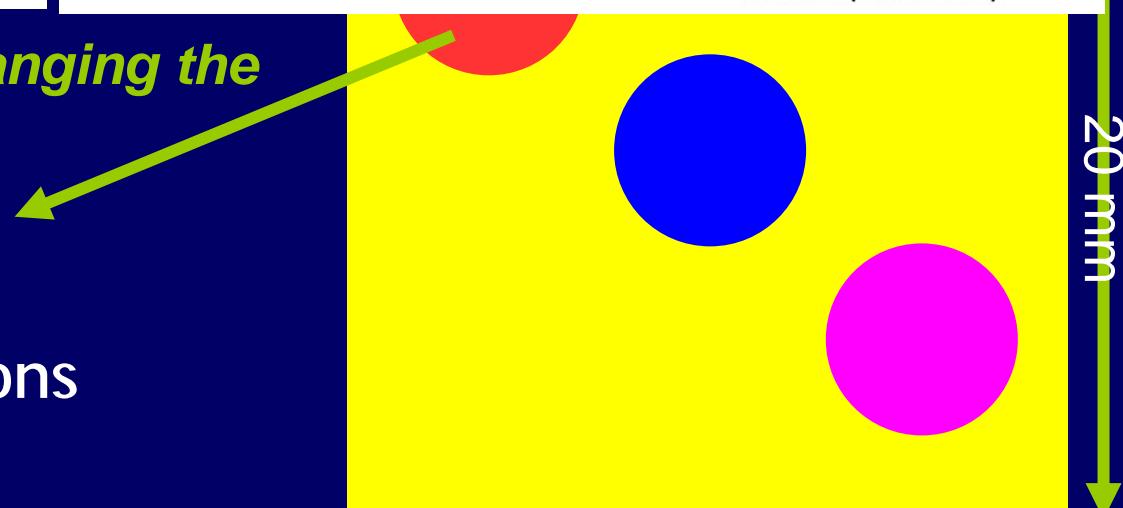


Trise of elastic scattering (Xe@35AMeV) vs fluence STOPPED EVENTS



Keeping the field constant by changing the bias Voltage

Heavy damage zone:
 $6 \times 10^8 / \text{cm}^2$ implanted Xe ions



FAZIA: RADIATION DAMAGE

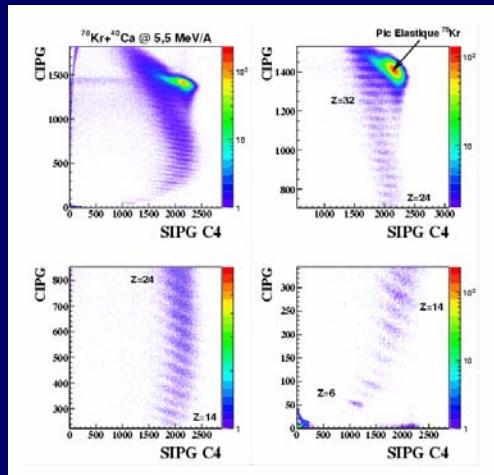
LNS (November 2009): Radiation damage and PSA

- The average effect of the increased reverse current (associated to local damage) can be fully recovered by simply keeping the field constant
- No significant effect is expected for the electronic noise (below 100 keV)
- Local damage is mainly associated to mono-energetic implanted ions (a narrow trapping layer is created at a depth="ion range"):
 - 2×10^7 (Xe-like) ions per detector (4cm^2) is the estimated limit for full Fazia performance for the energy and PSA of the same considered ions
 - minor degradation is observed in zones where ions have punched-through and fluences about 10^2 times higher can be sustained

NUCLEAR EQUATION OF STATE

$E(\rho, (N-Z)/A, T)$

INDRA@SPIRAL



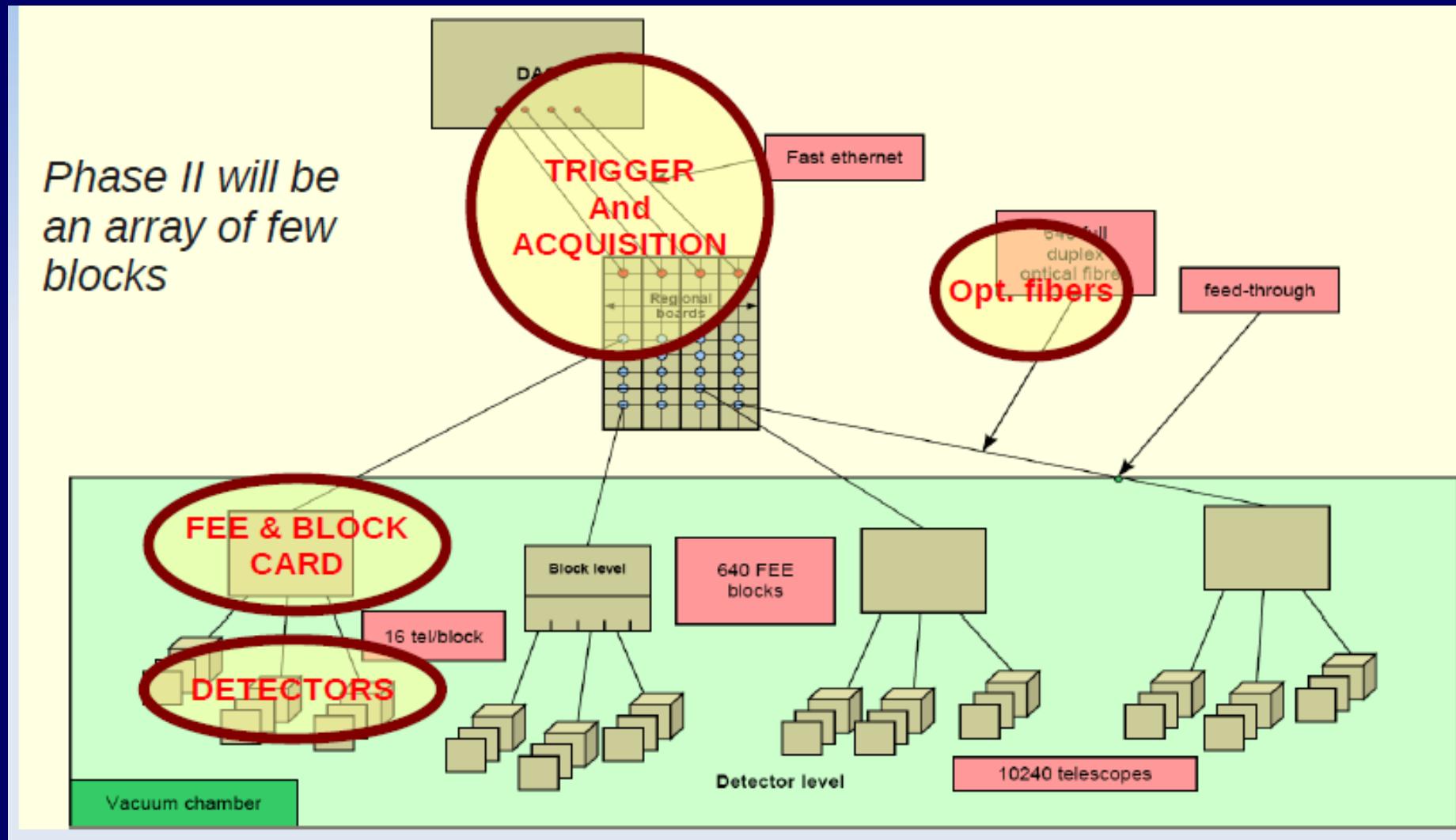
*Fragment production
at 5.5 A.MeV*

LIQUID PHASE

**Isospin physics case from
SPIRAL2/SPES (liquid phase)
to GANIL/LNS high energies**

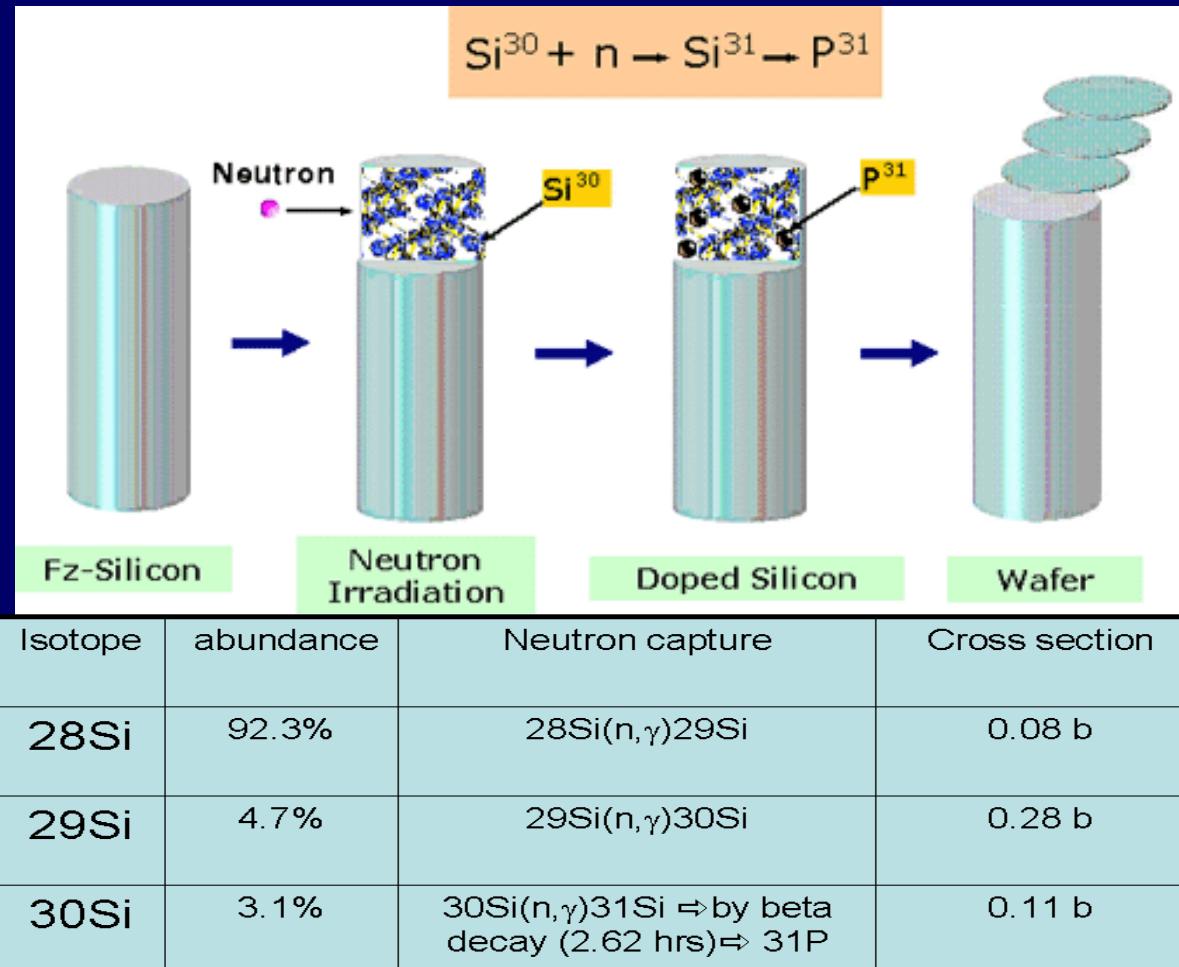
FAZIA Phase2 2011-2013

Phase2 = “répétition générale” for several 1000 of telescopes



FAZIA PhaseI-R&D

Beyond $\Delta E-E$: Z and A Identification with Pulse Shape
Doping uniformity: nTD-silicon detector

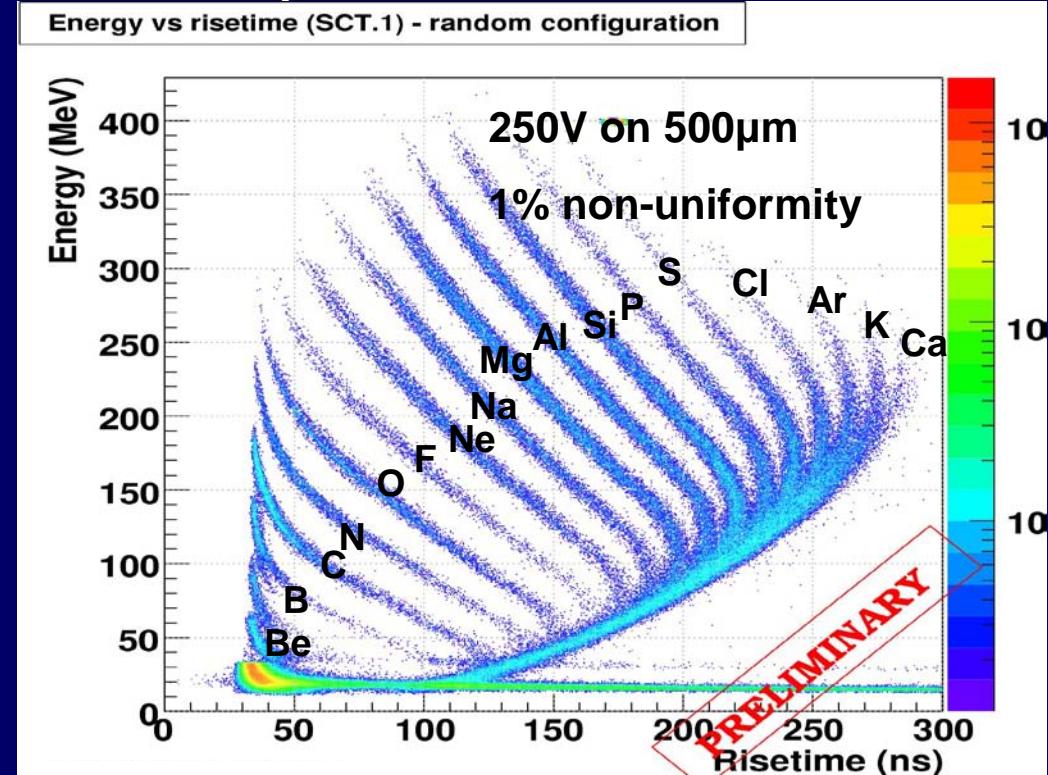
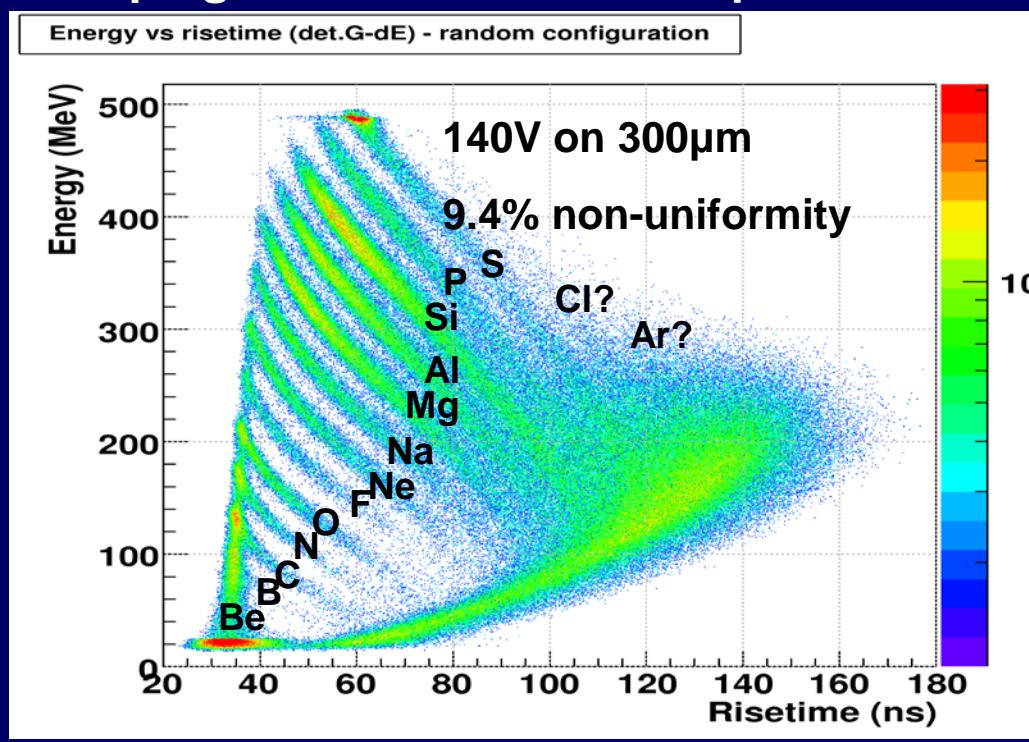


Regular Silicon: +/- 15% uniformity – “regular” nTD silicon: below +/- 5%
FAZIA nTD silicon: +/- 0.5%

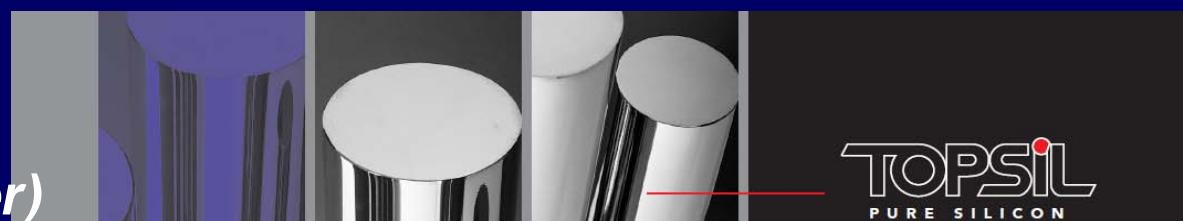
FAZIA PhaseI-R&D

Beyond $\Delta E-E$: Z and A Identification with Pulse Shape
Doping uniformity: nTD-silicon detector

DIGITAL PULSE SHAPE on 500 μ m and 300 μ m Silicons with similar field and different doping non-uniformities: 300 μ m: ~ 4 GeV full scale 500 μ m: ~ 4 GeV full scale



+/- 5% is not enough PSId.
needs +/- 0.5%

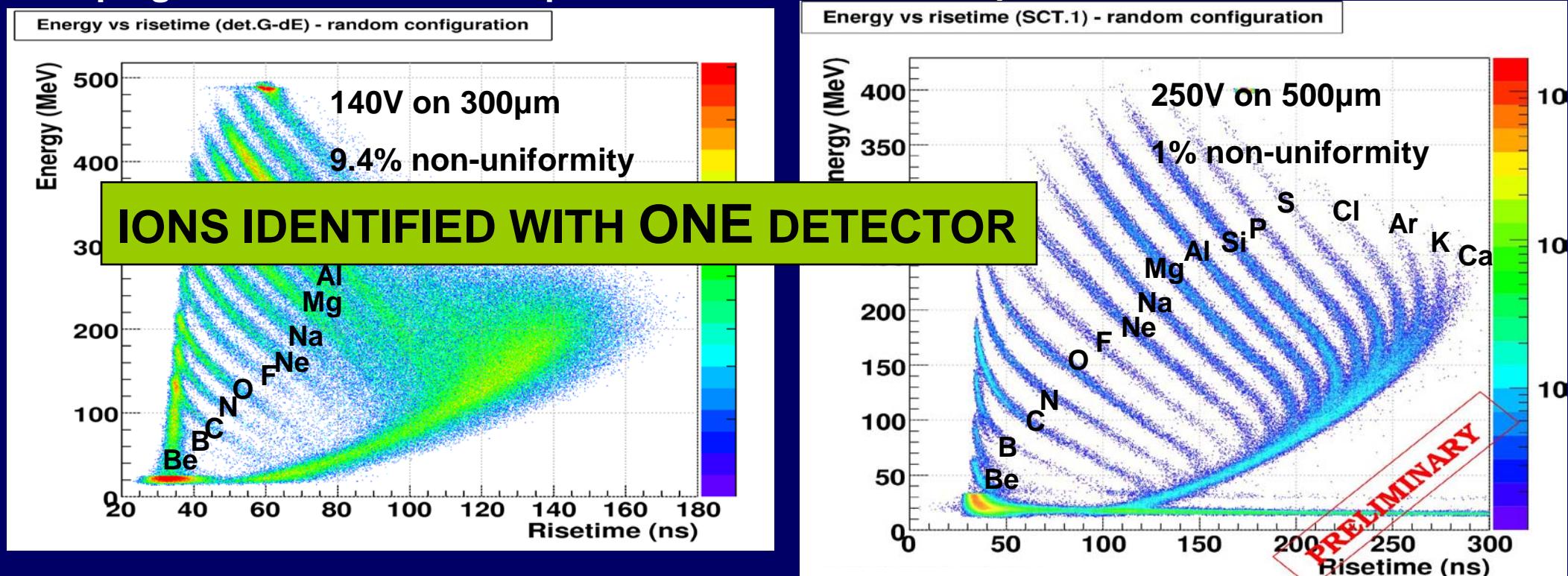


It is possible (work with manufacturer)

FAZIA PhaseI- R&D

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Doping uniformity: nTD-silicon detector

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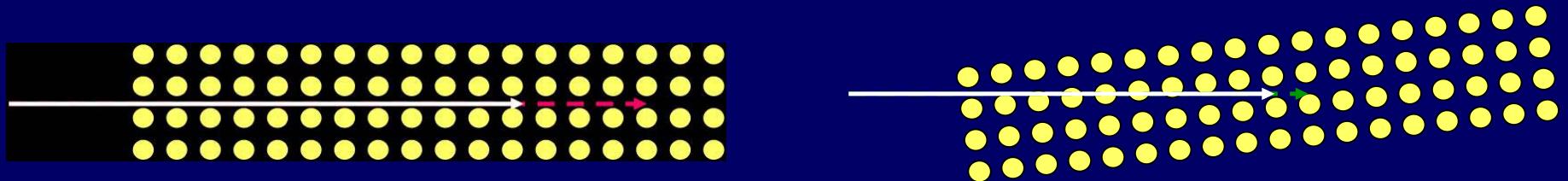


+/- 5% is not enough PSId.
needs +/− 0.5%

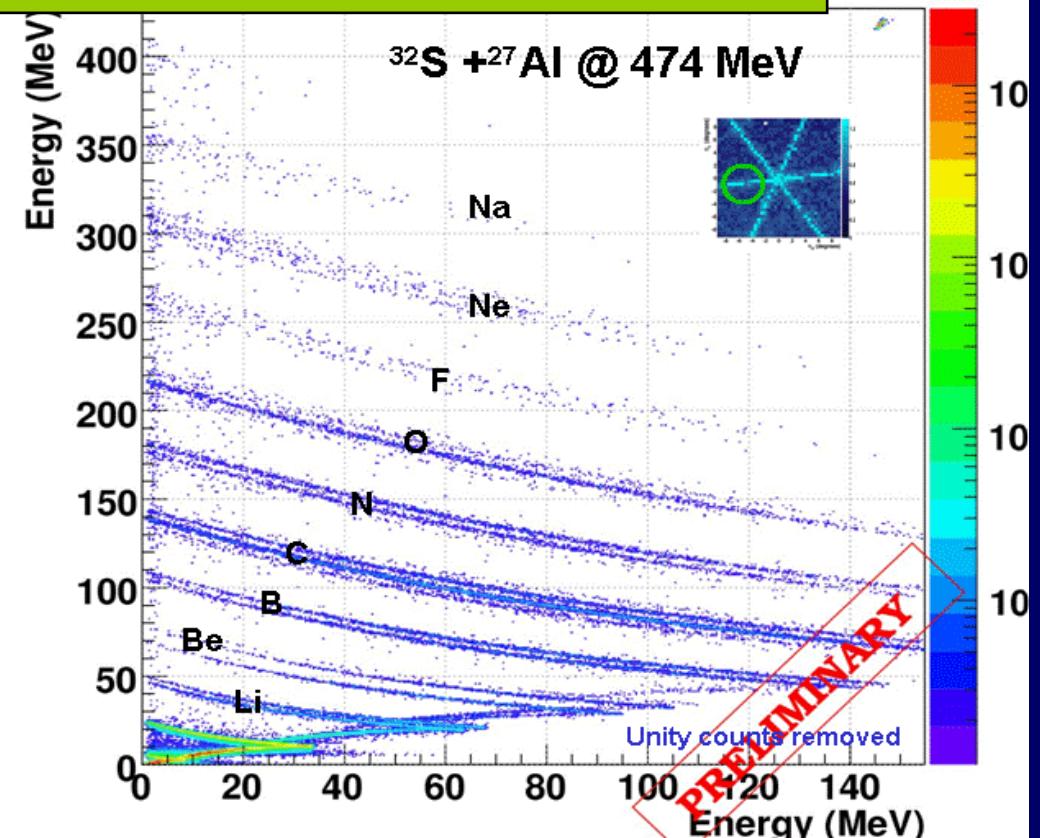
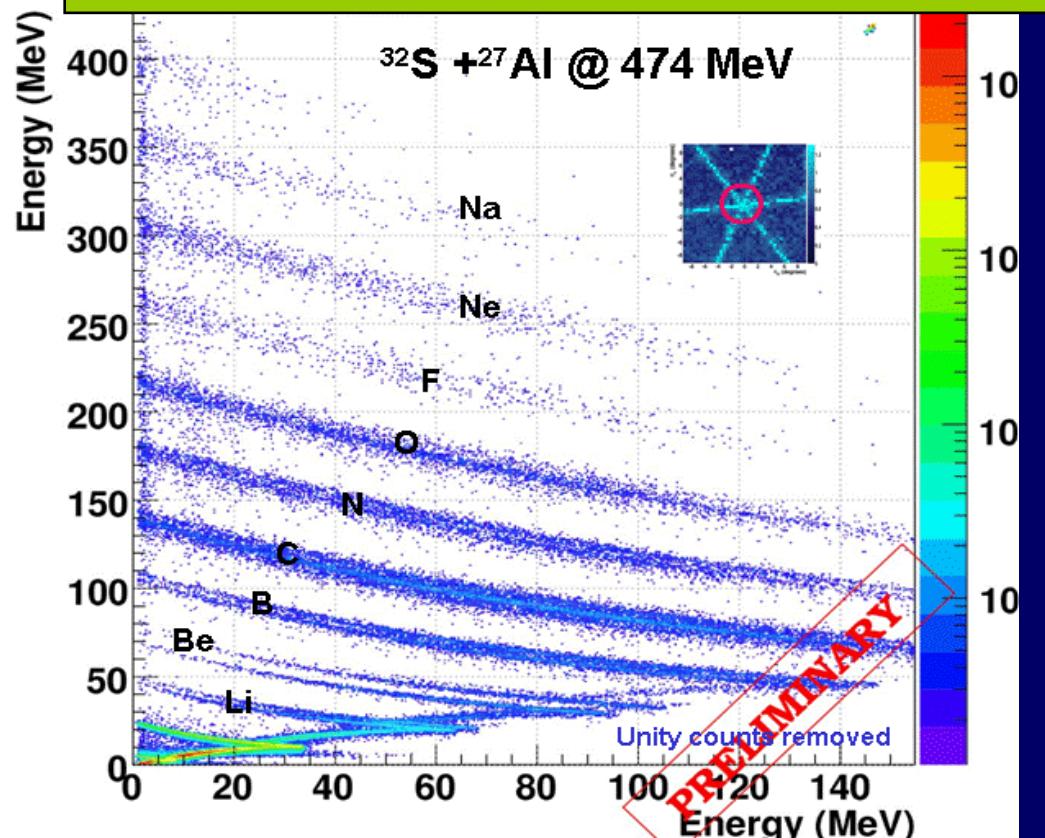
It is possible (work with manufacturer)



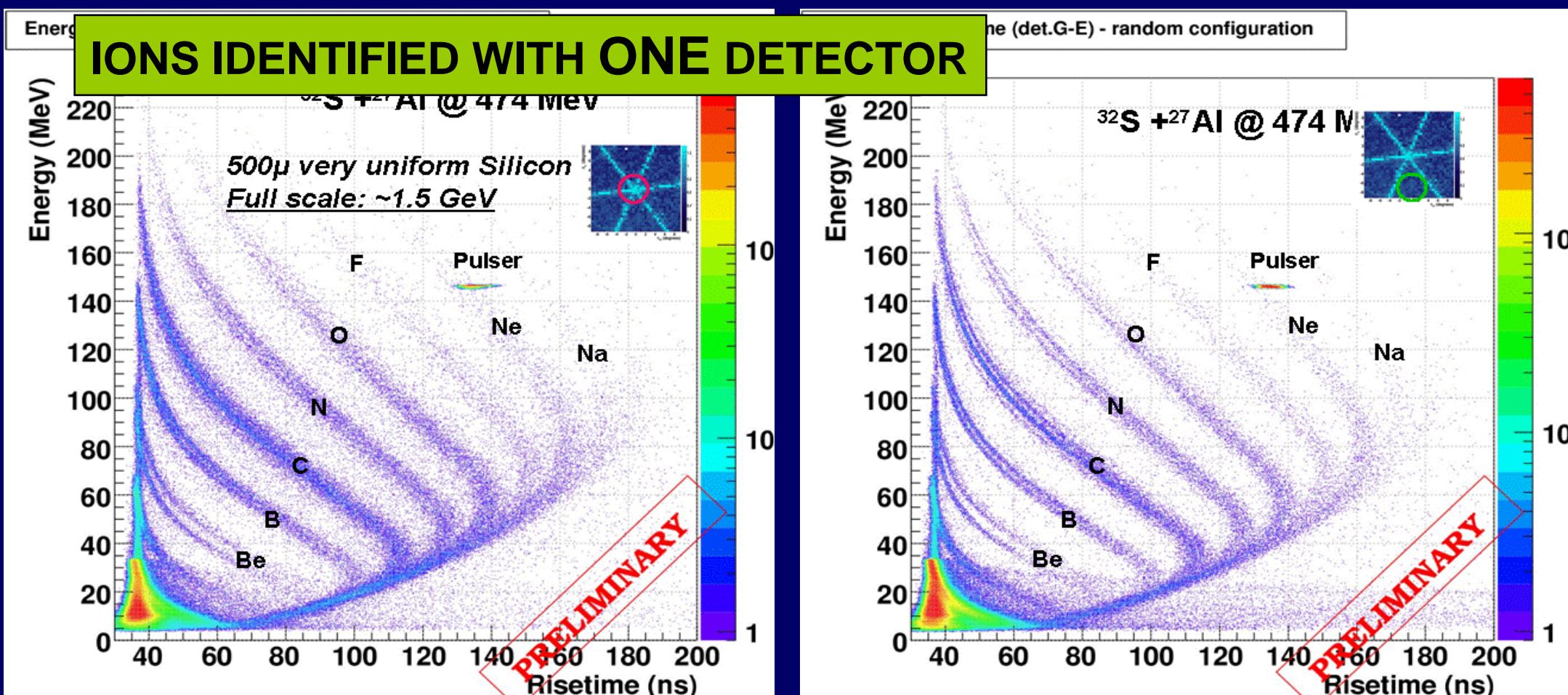
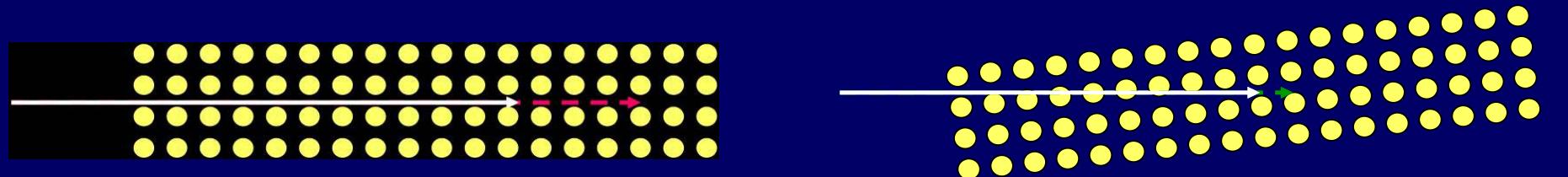
FAZIA PhaseI-R&D



IONS IDENTIFIED WITH TWO DETECTORS: USUAL DE/E-plot



FAZIA PhaseI-R&D



LNL-Experiment